

Emergent ferromagnetism near three-quarters filling in twisted bilayer graphene

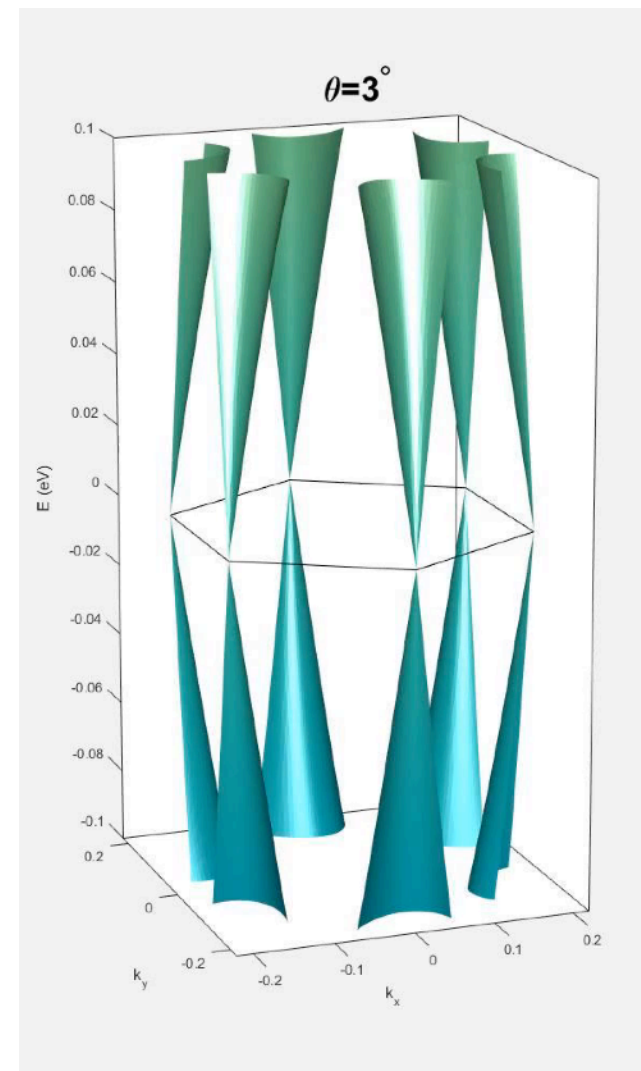
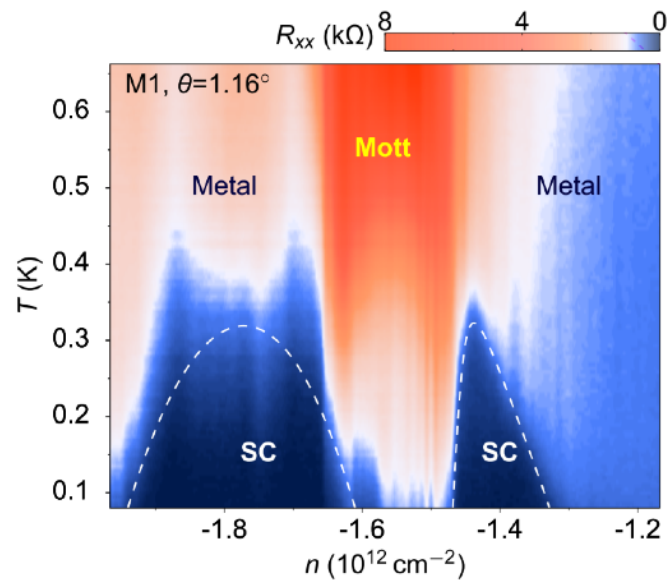
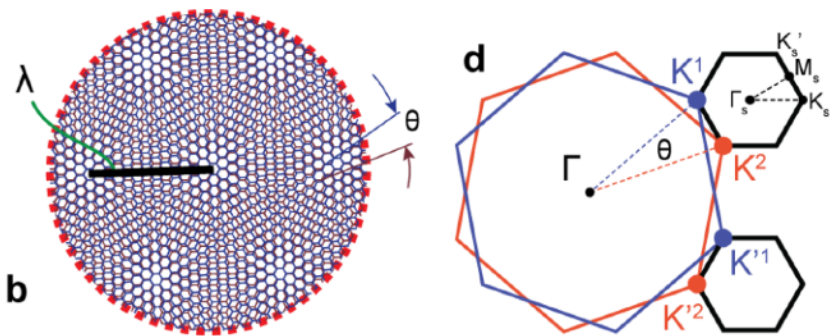
David Goldhaber-Gordon

KITP 1/14/2019

arXiv 1901.03520

Strong Correlations

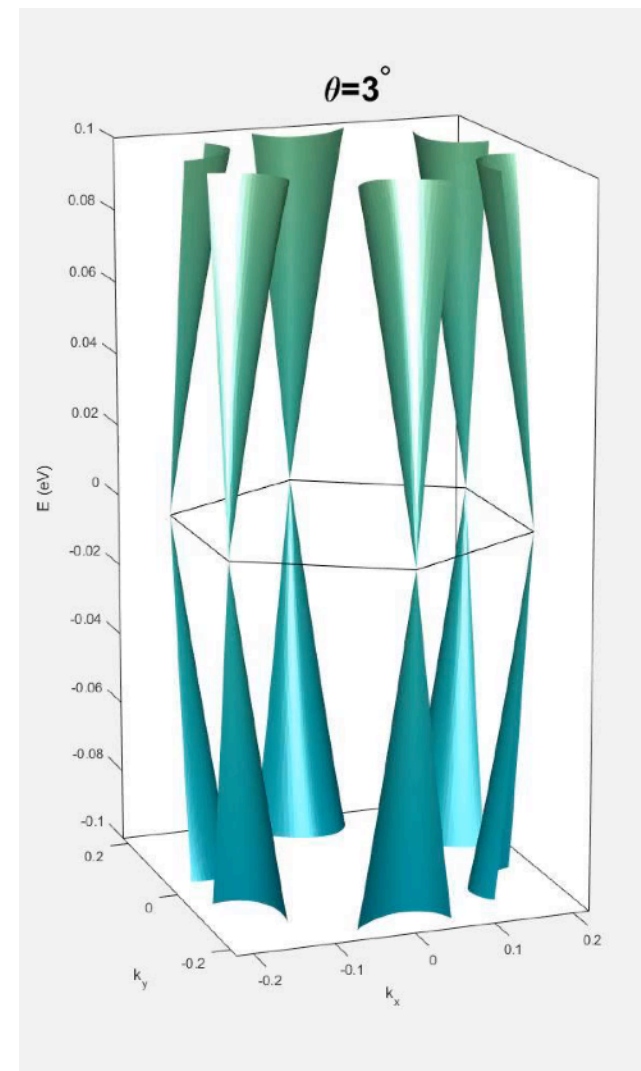
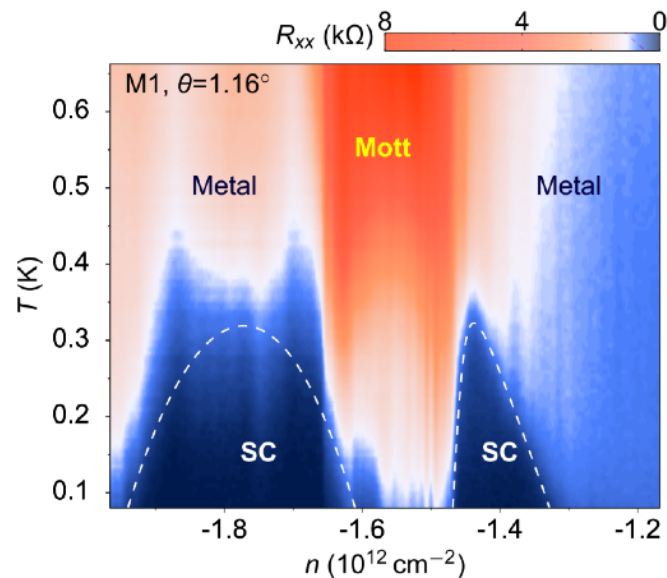
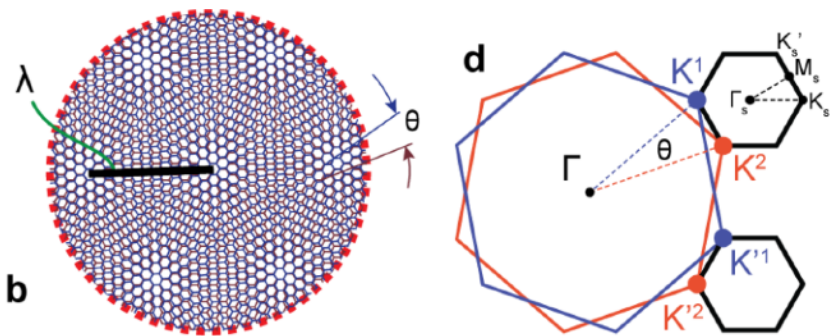
Twisted layer graphene and hBN provide unprecedented control of correlations in 2D electron systems



Cao, *Nature* (2018)
cf Nam, Koshino PRB (2017)
Morell (2010)
Bistritzer (2011)

Strong Correlations

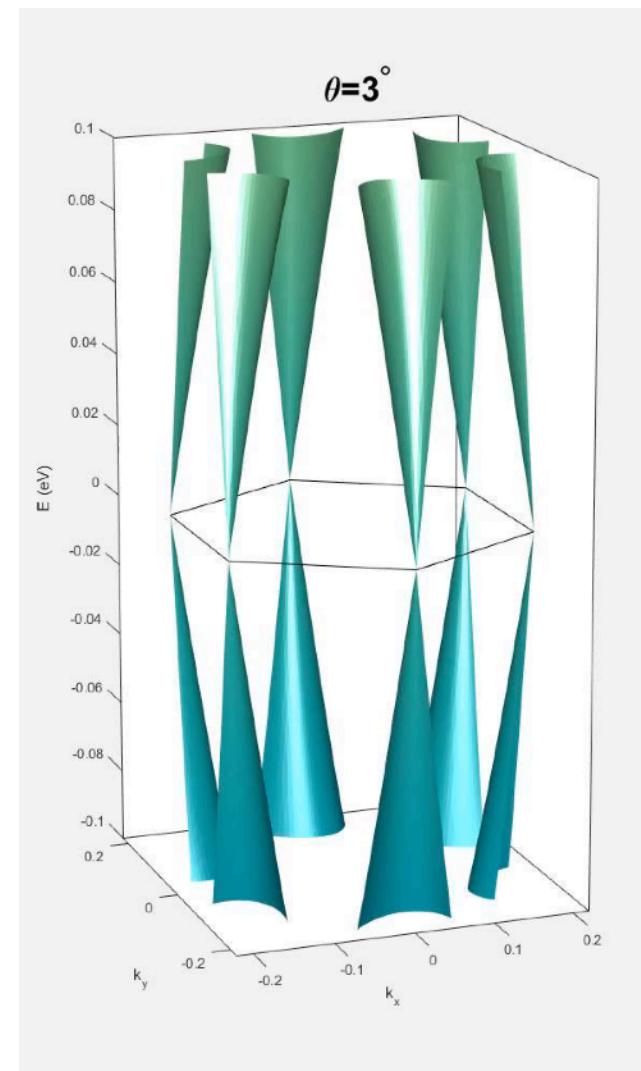
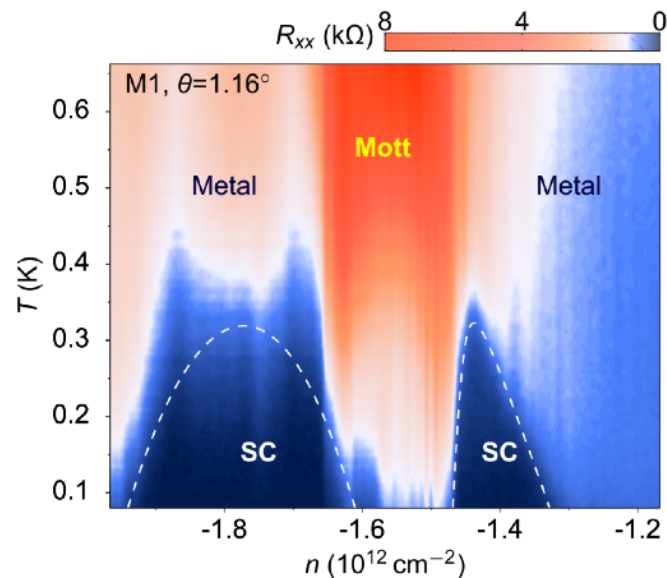
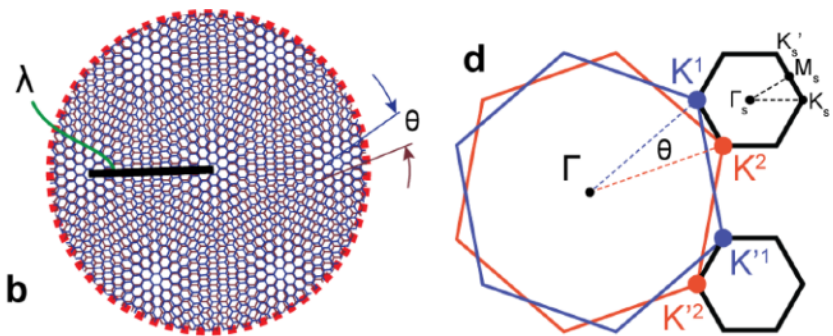
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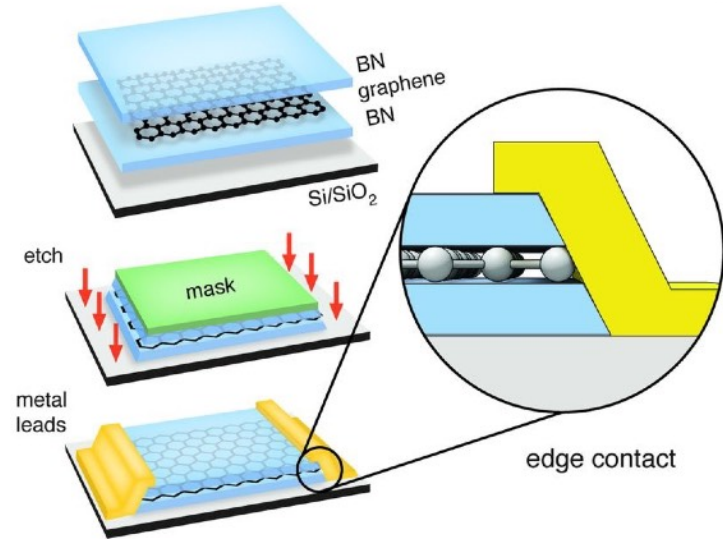
Strong Correlations

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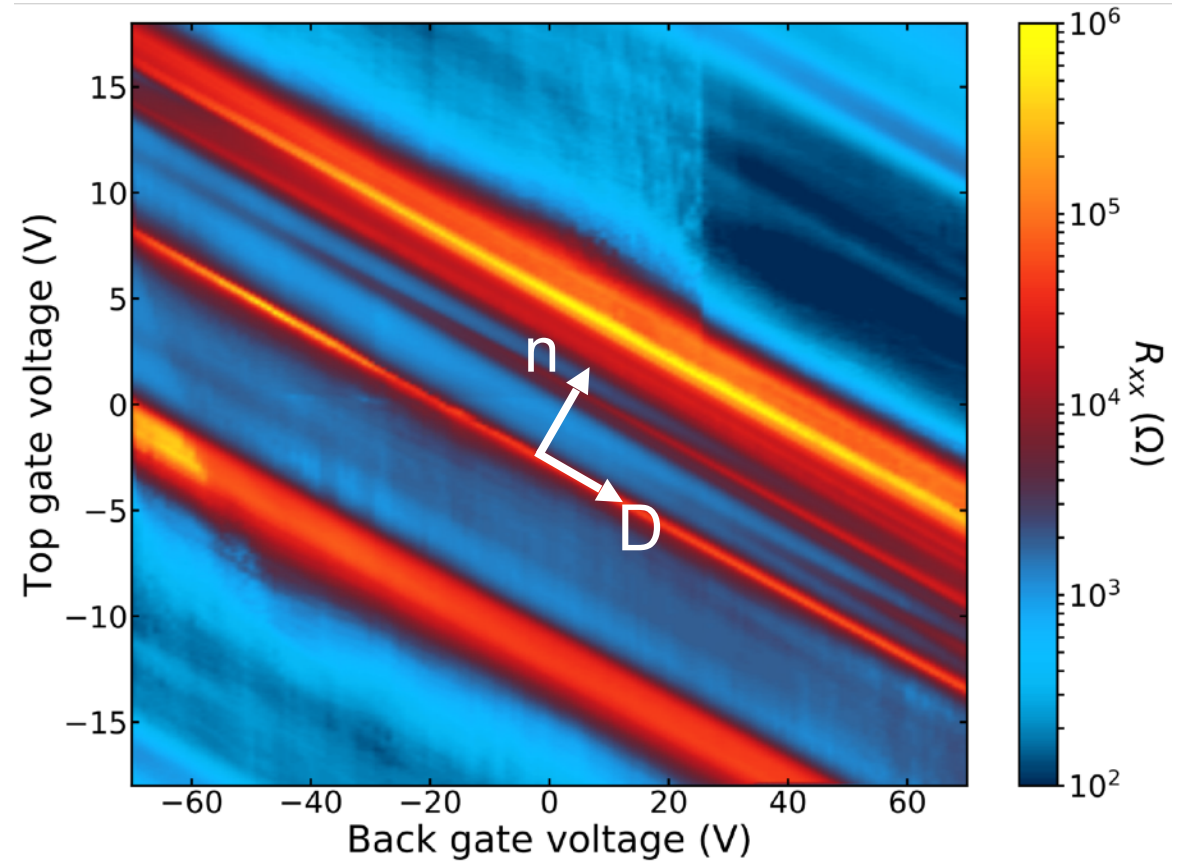
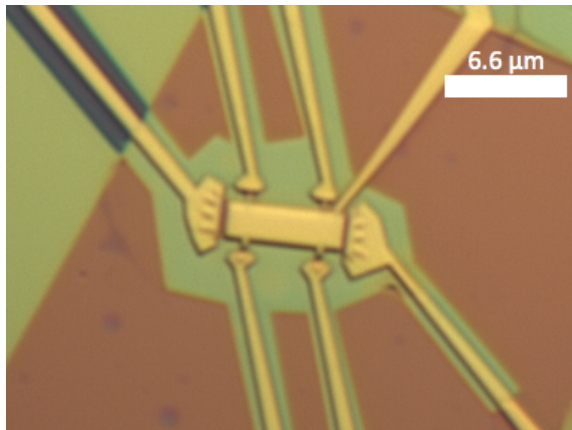


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Strong Correlations: Twisted bilayer near magic angle



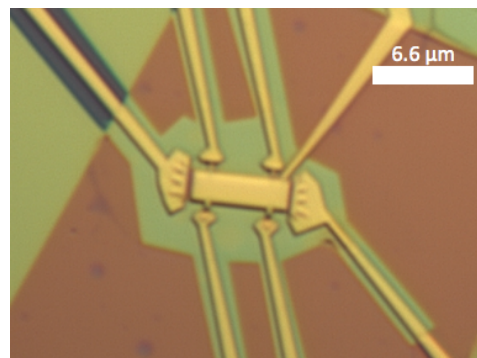
Wang, *Science* (2013)



Angle $1.20 \pm 0.01^\circ$. Target 1.17°

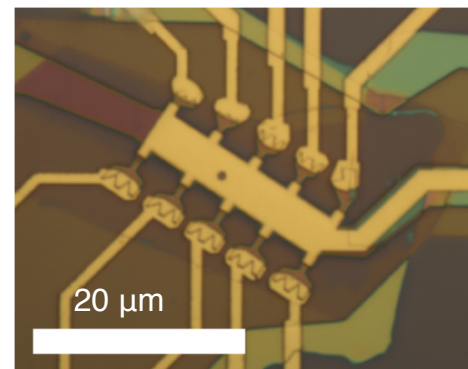
Alignment with hBN matters?

Device 1: aligned hBN

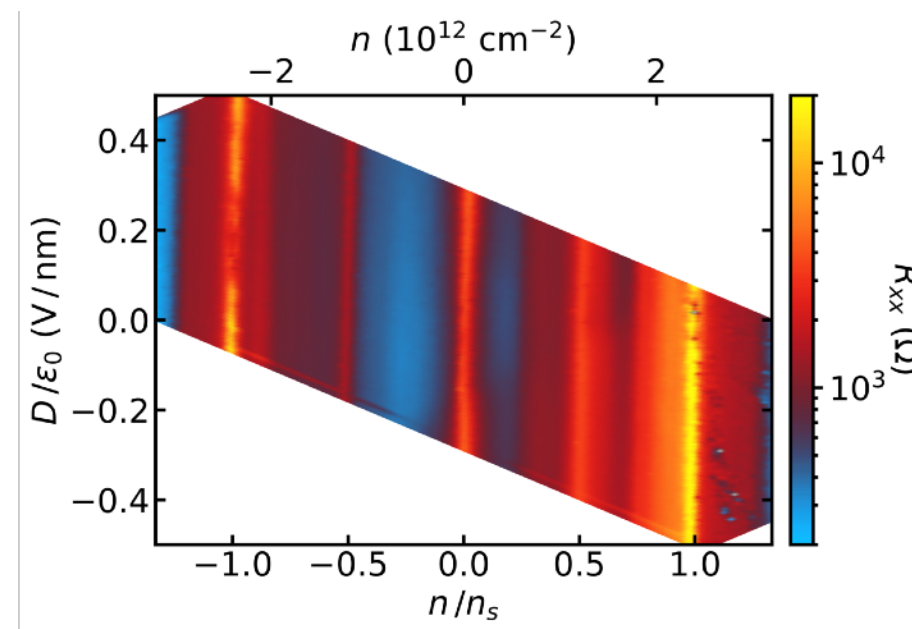
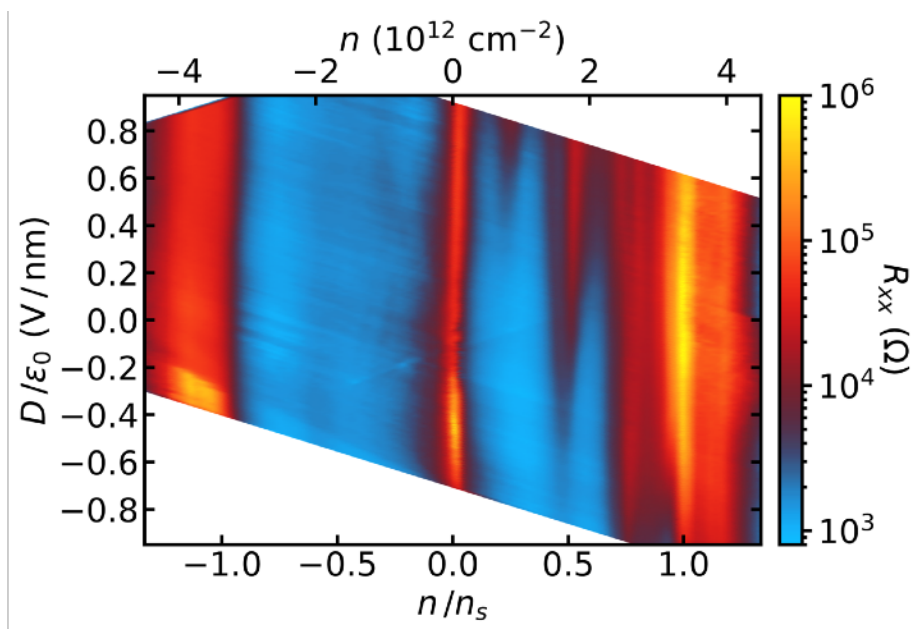


Graphene twist $1.20 \pm 0.01^\circ$
Twist to one hBN $0.81^\circ \pm 0.02^\circ$

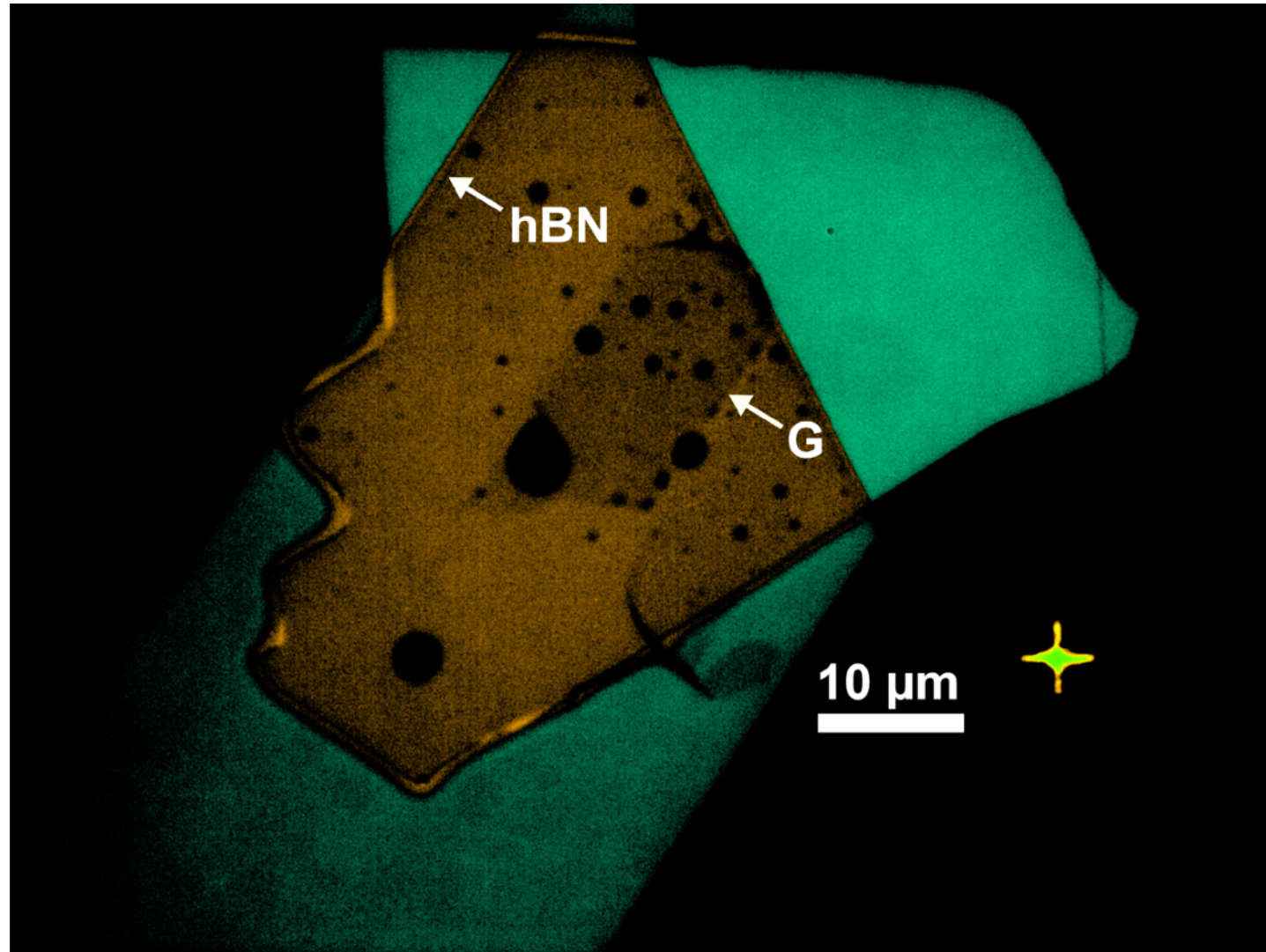
Device 2: misaligned hBN



Graphene twist $1.05 \pm 0.01^\circ$
Twist to hBN large

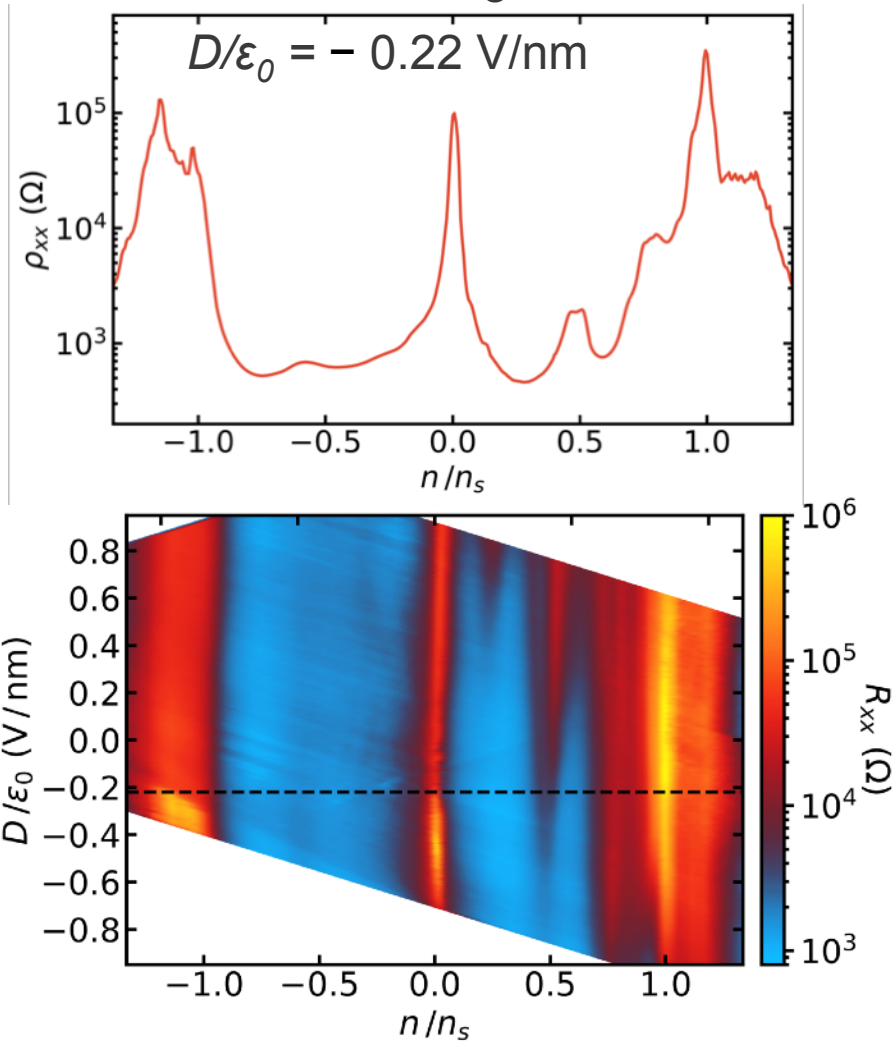


Visual hBN Alignment

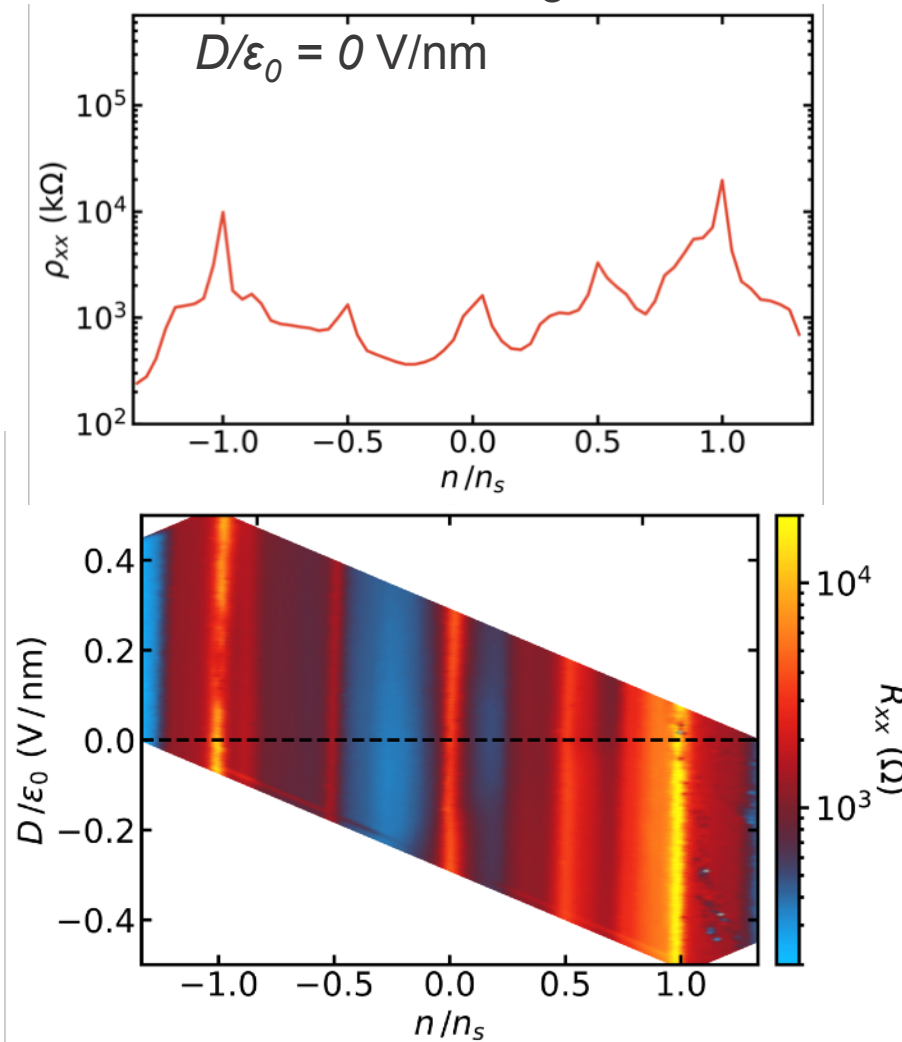


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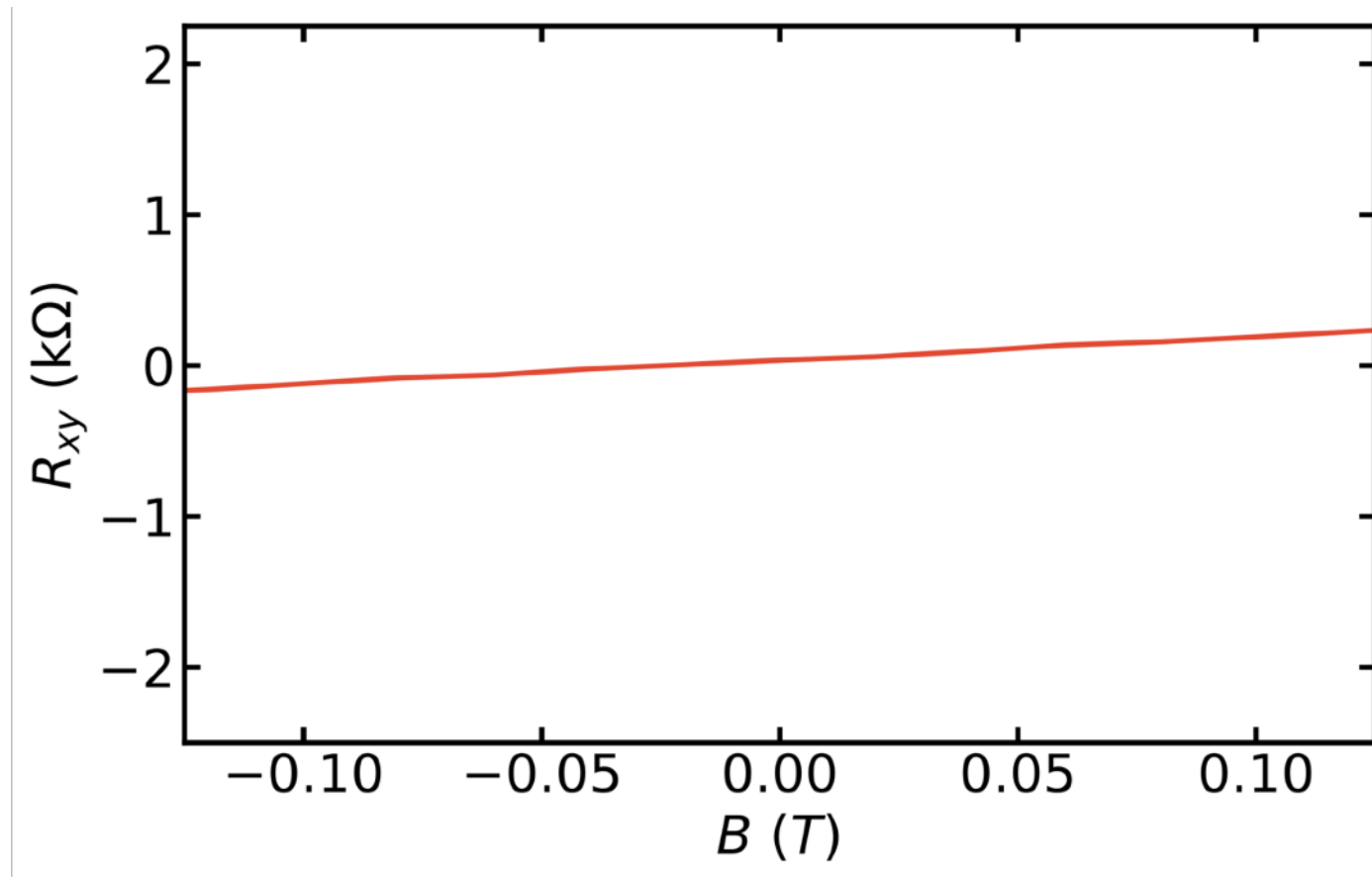


Device 2: misaligned hBN

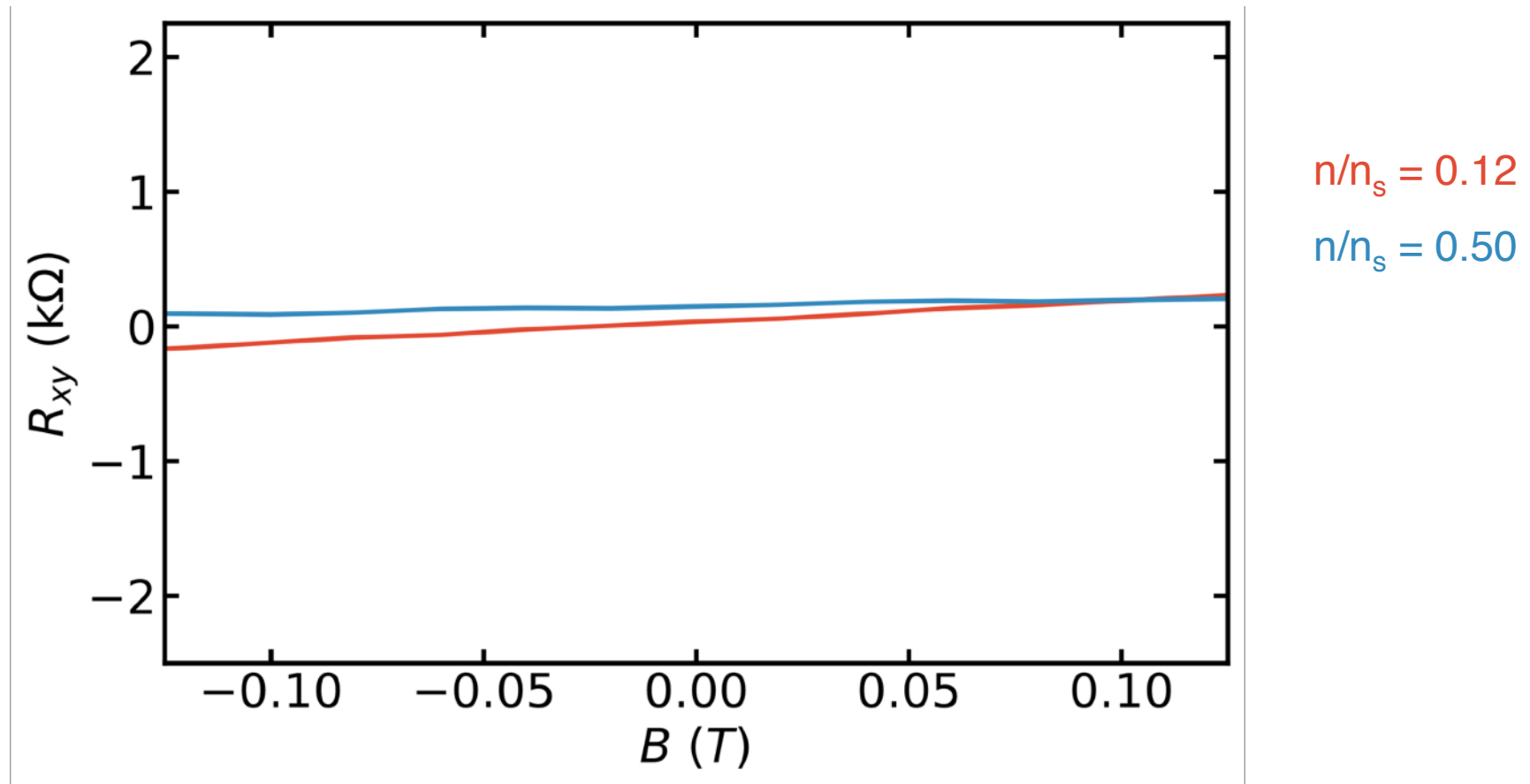


For insulating behavior and charge neutrality for graphene on hBN see
Amet PRL 110.216601
Hunt Science 1237240
(2013)

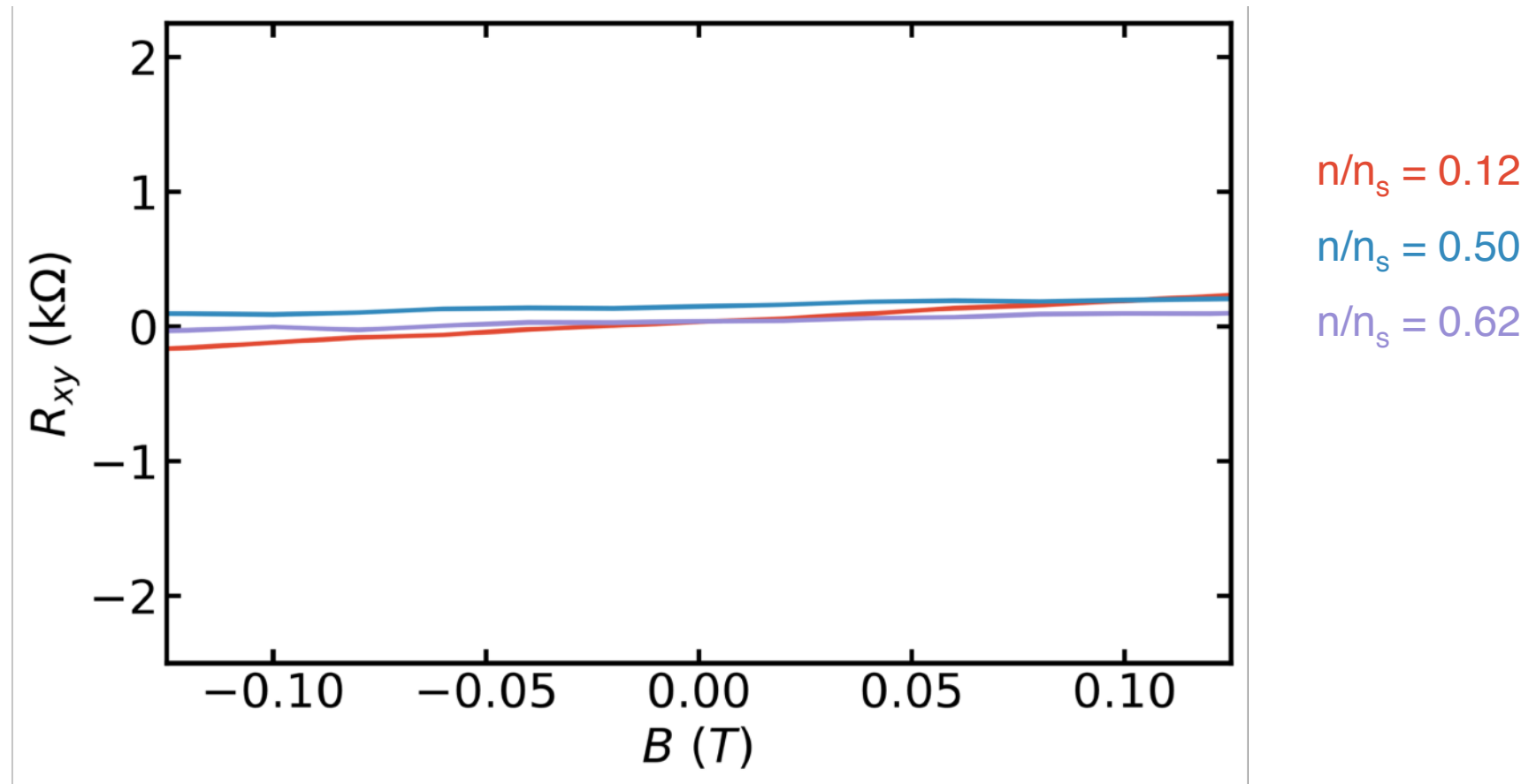
Measuring Hall Slope Density Dependence



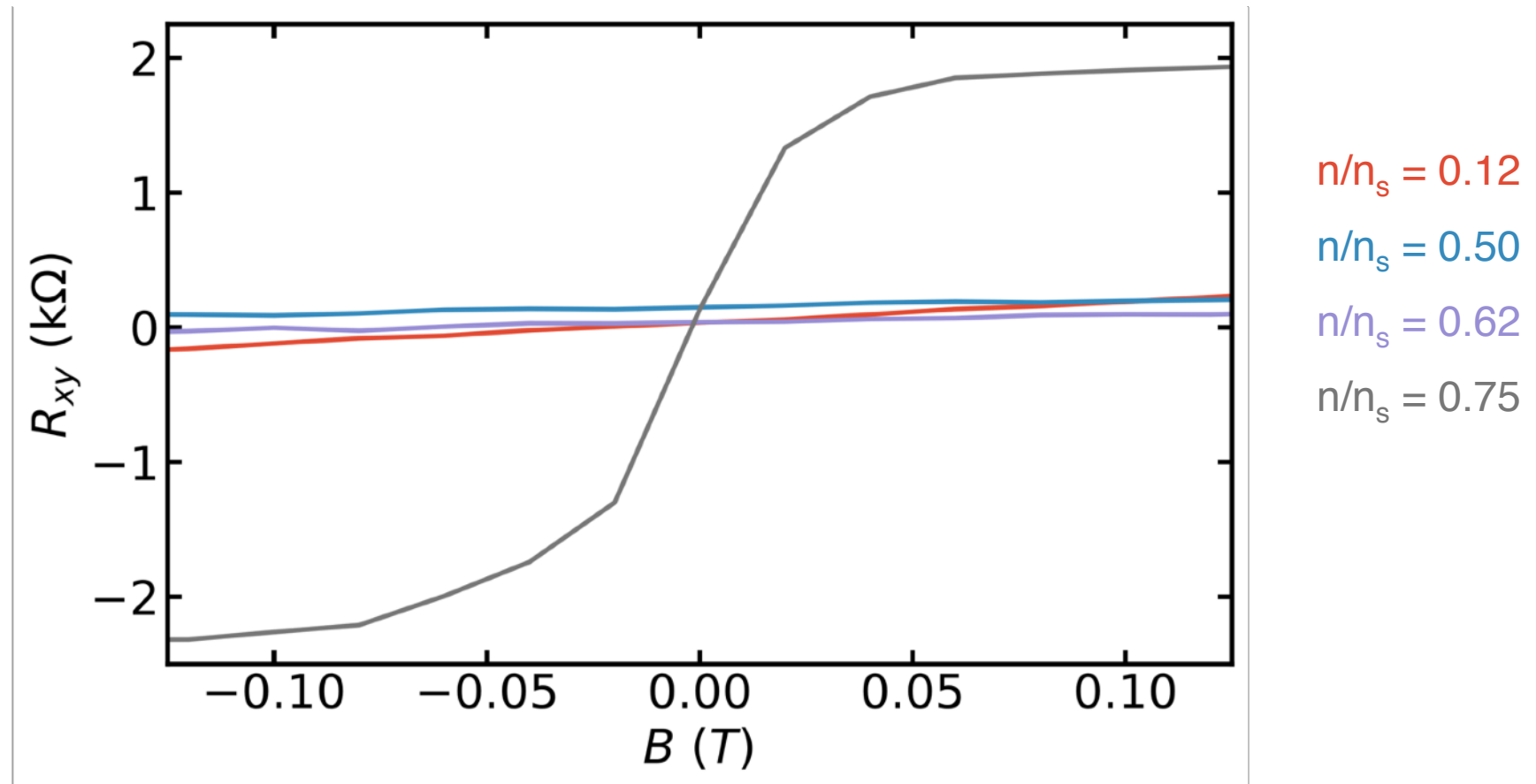
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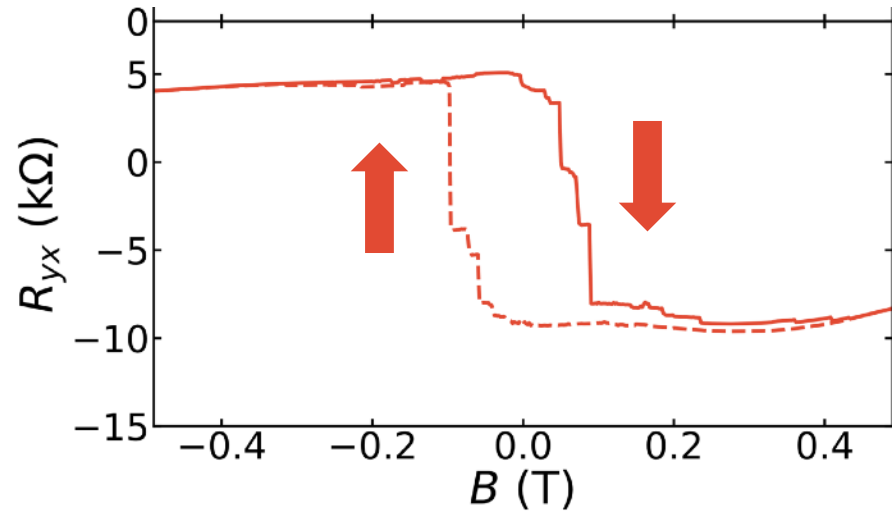
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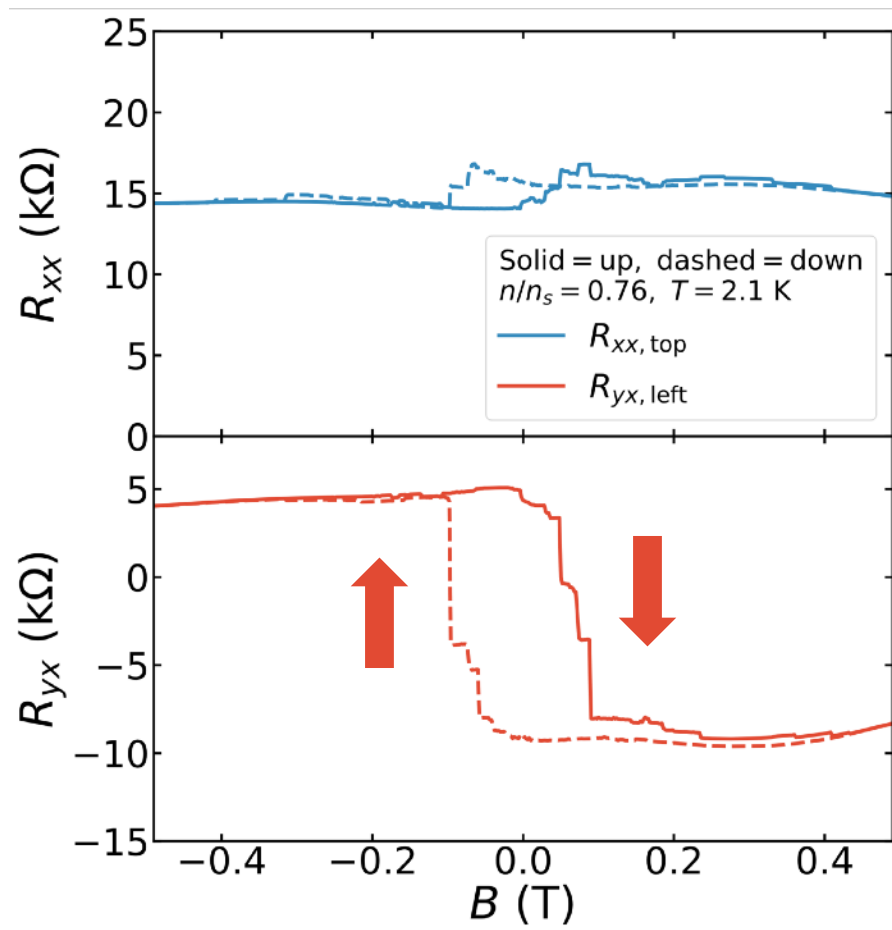
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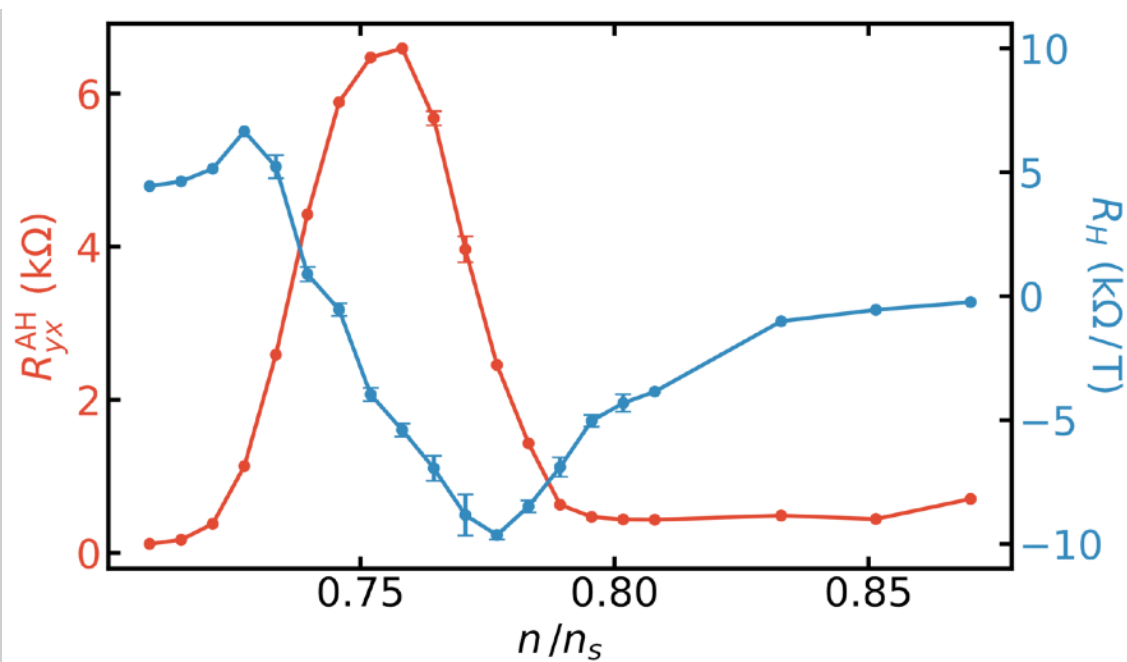
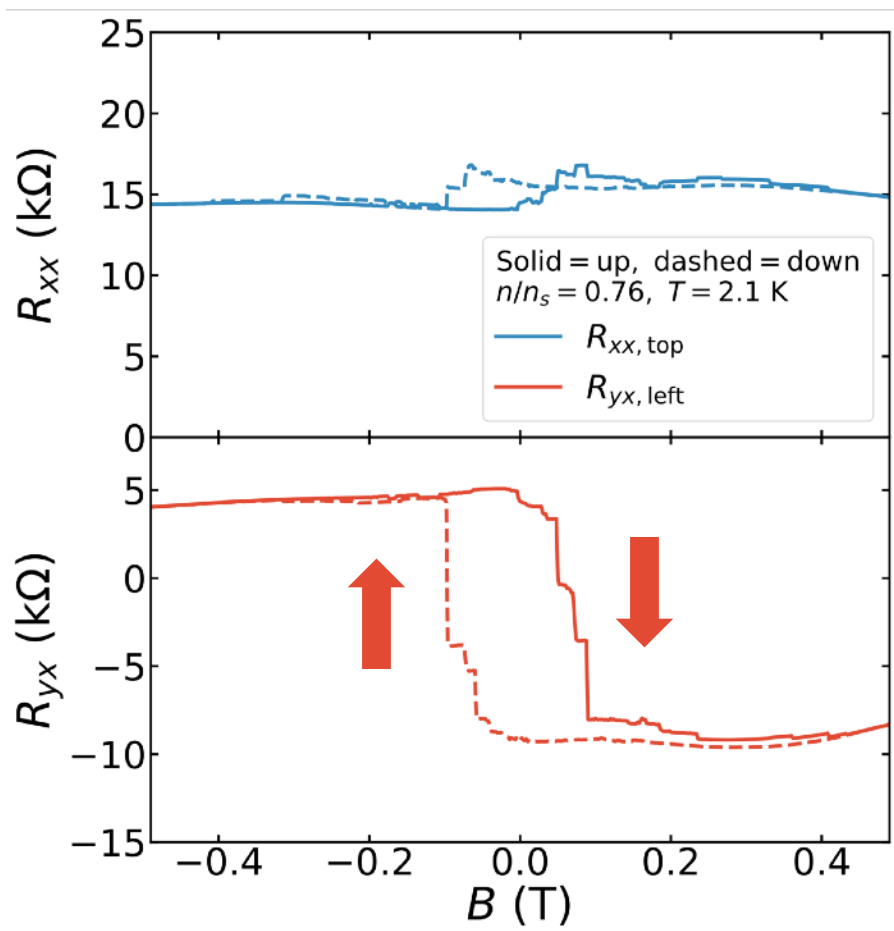
Emergent Ferromagnetism at $\frac{3}{4}$ Filling



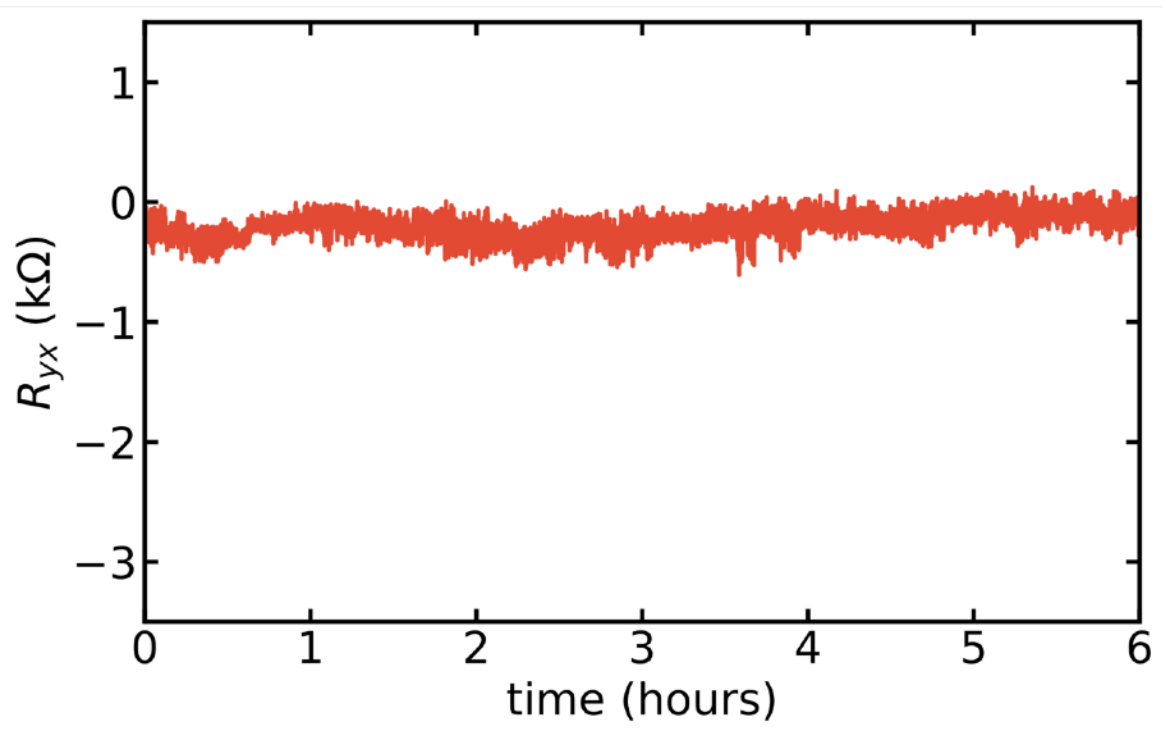
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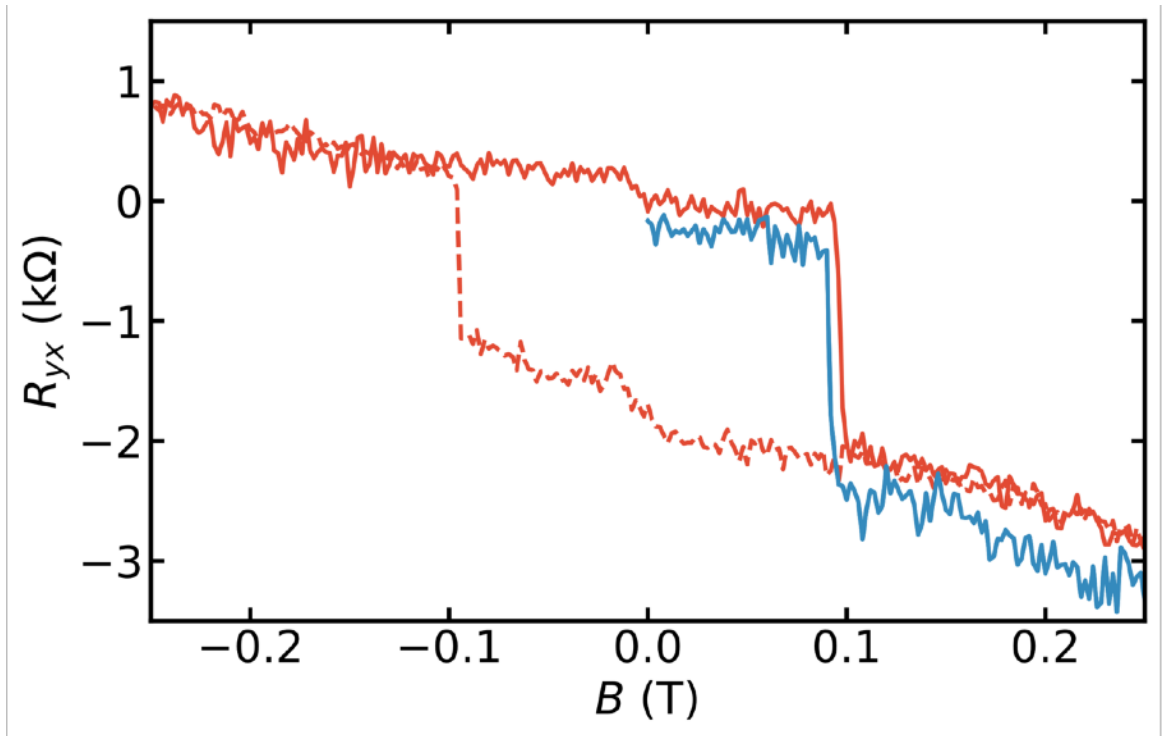
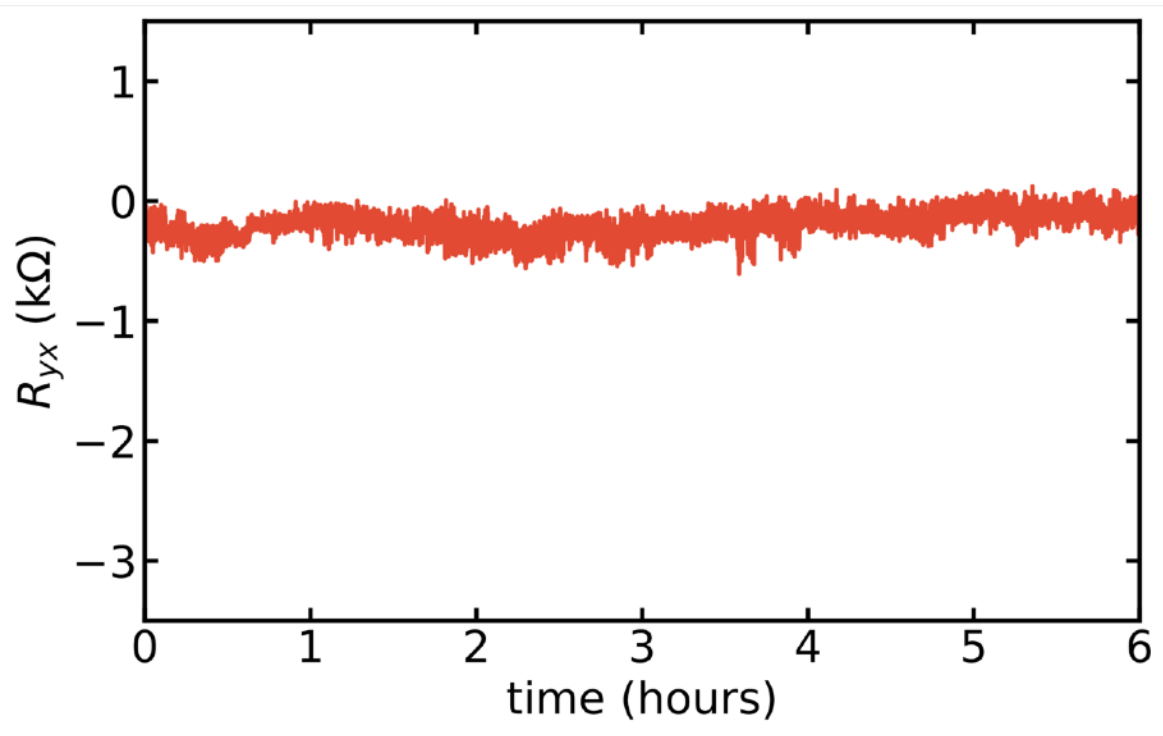
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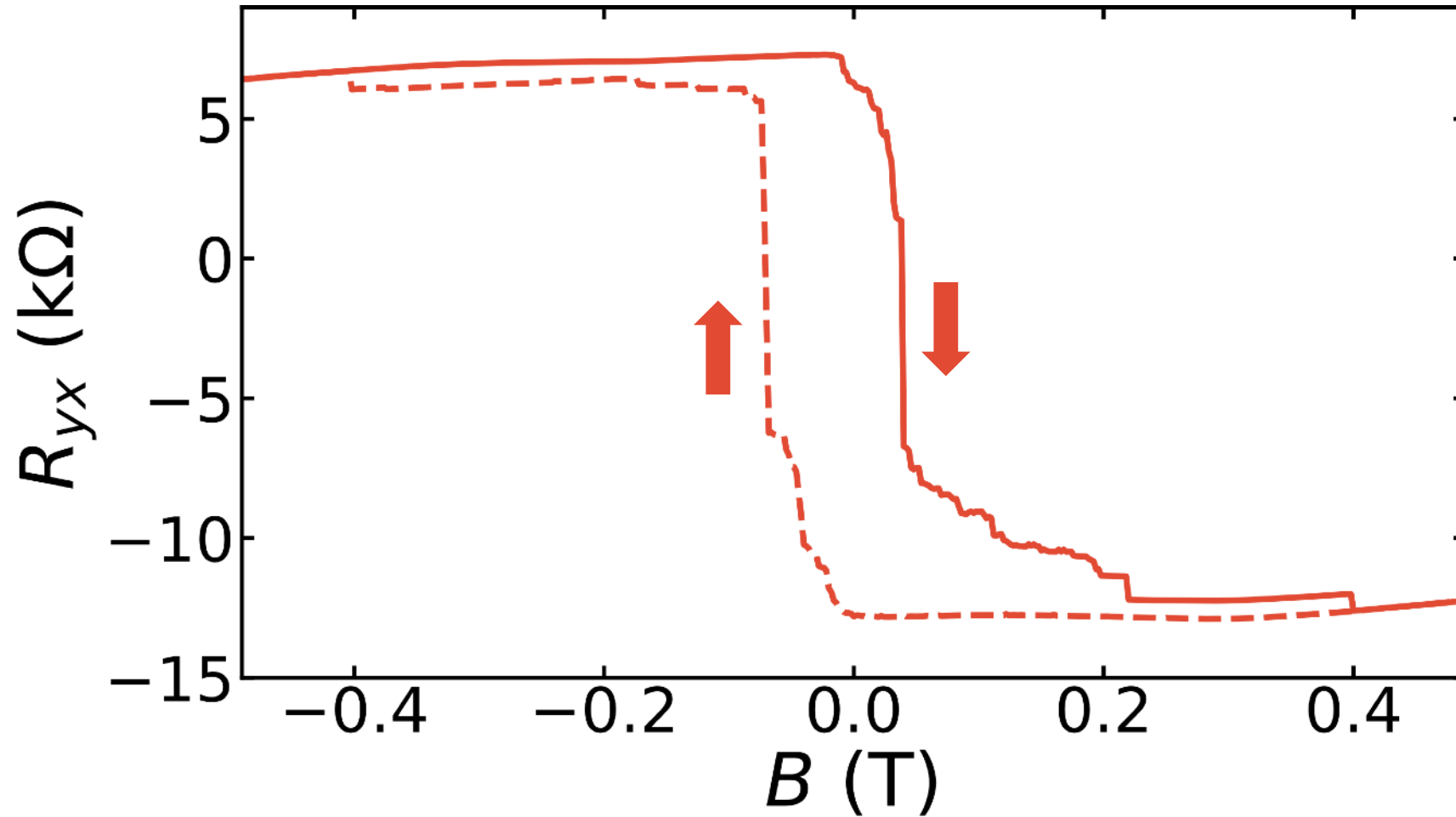
Magnetism is Stable with No Applied Field



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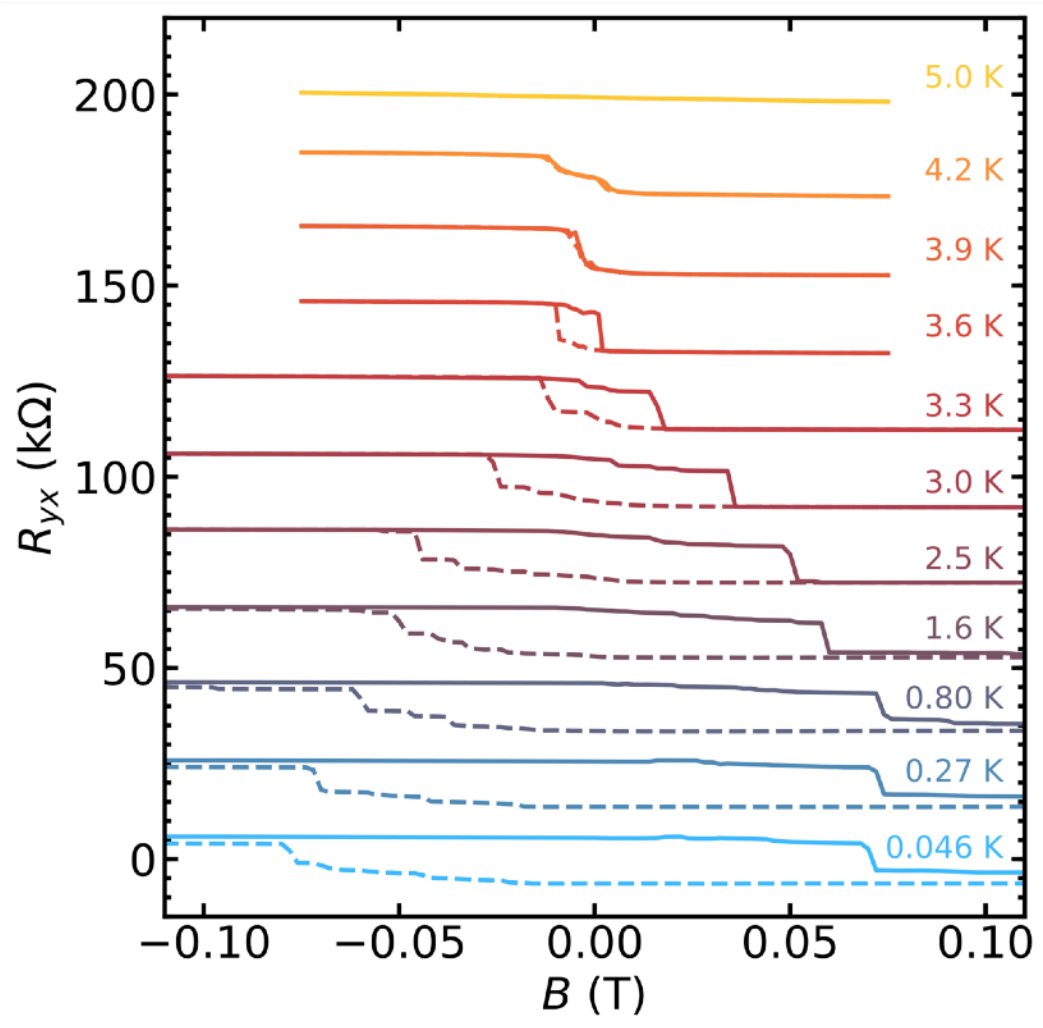


Anomalous Hall Signal Can Be Really Large!

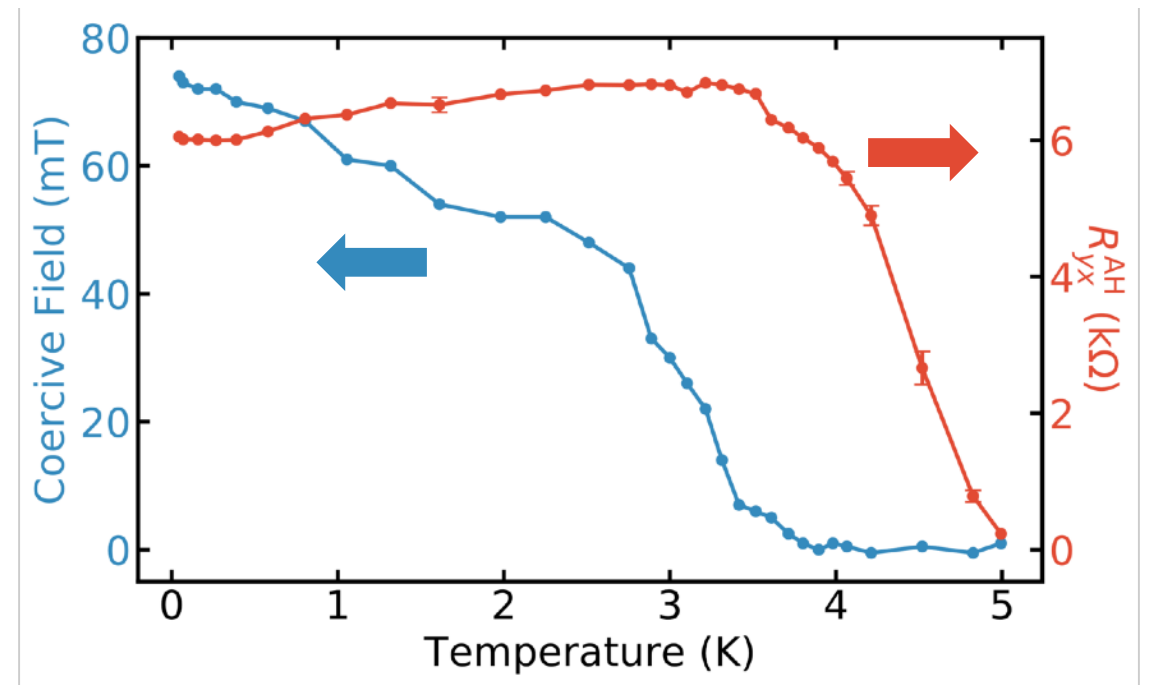
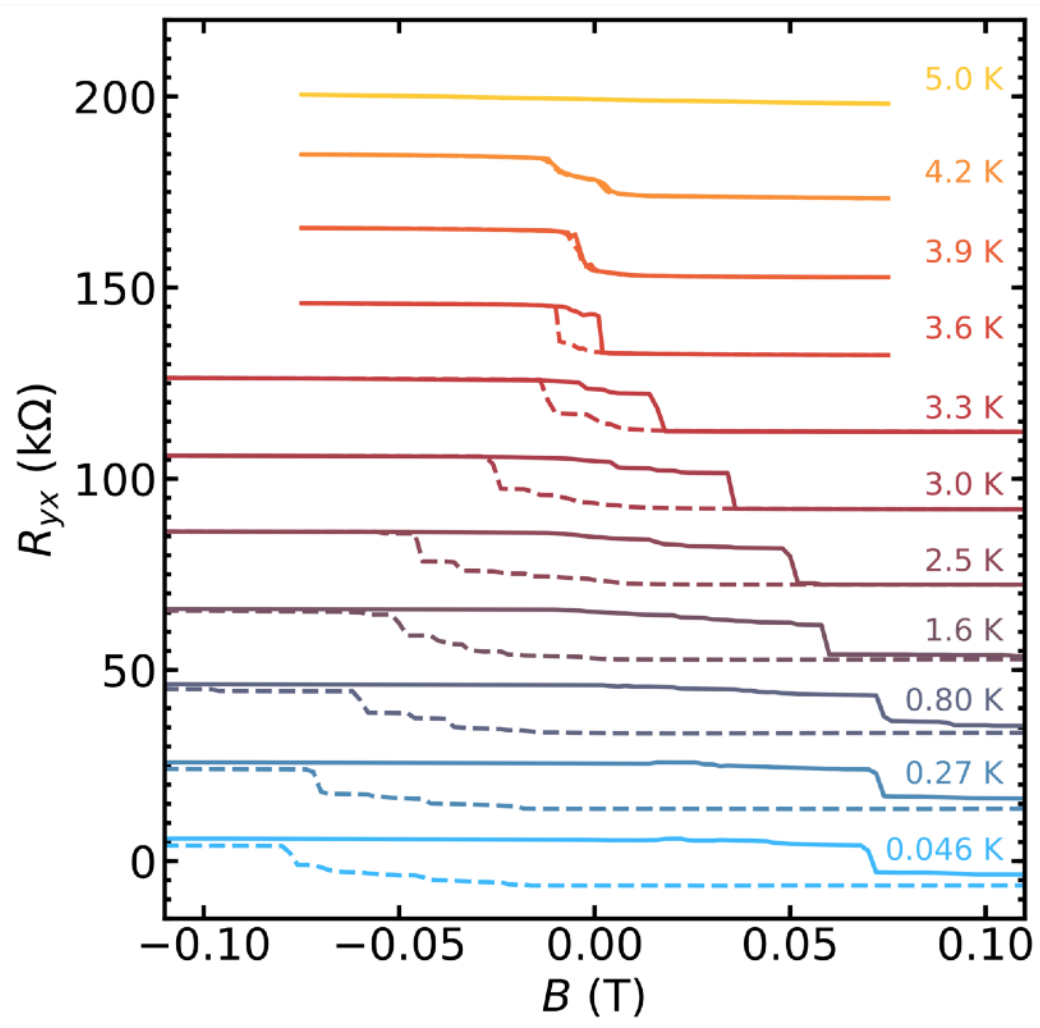


$n/n_s = 0.775$, $T = 2.1$ K

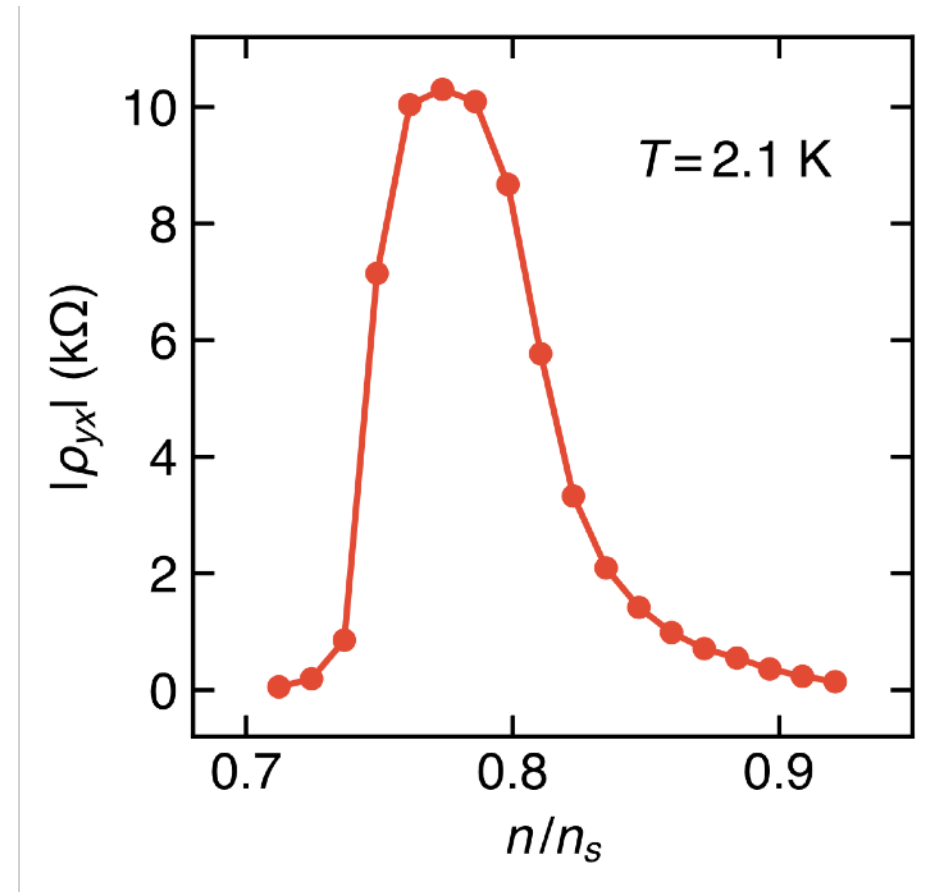
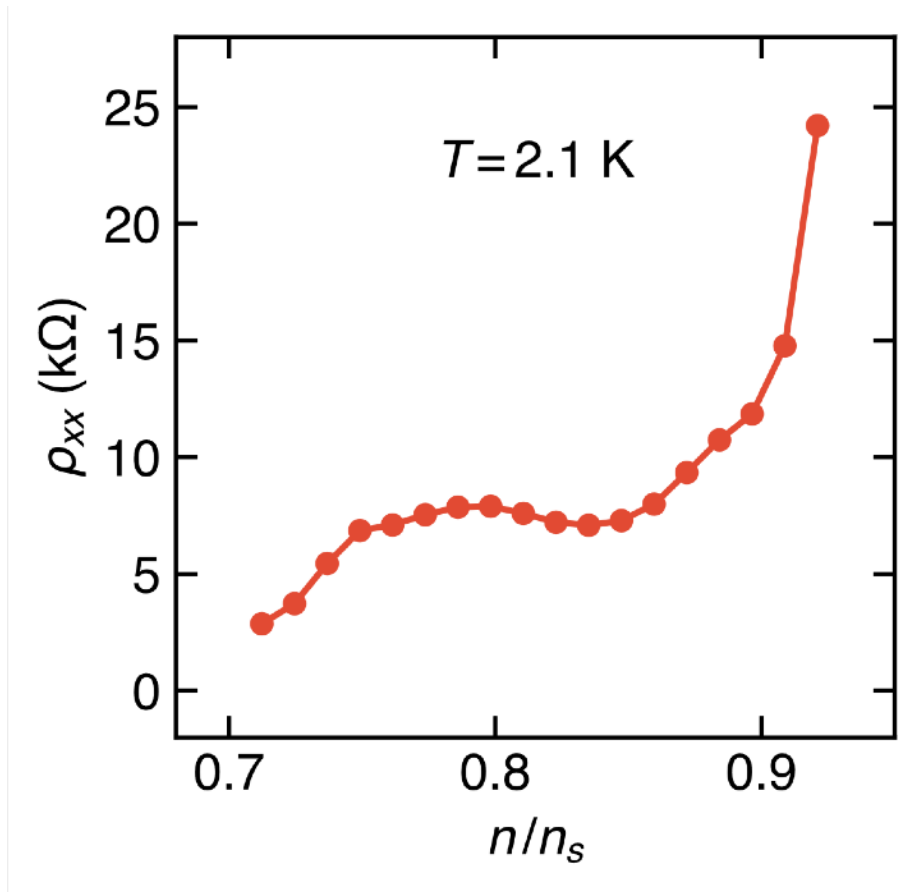
Temperature Dependence of Emergent Ferromagnetism at $\frac{3}{4}$ Filling



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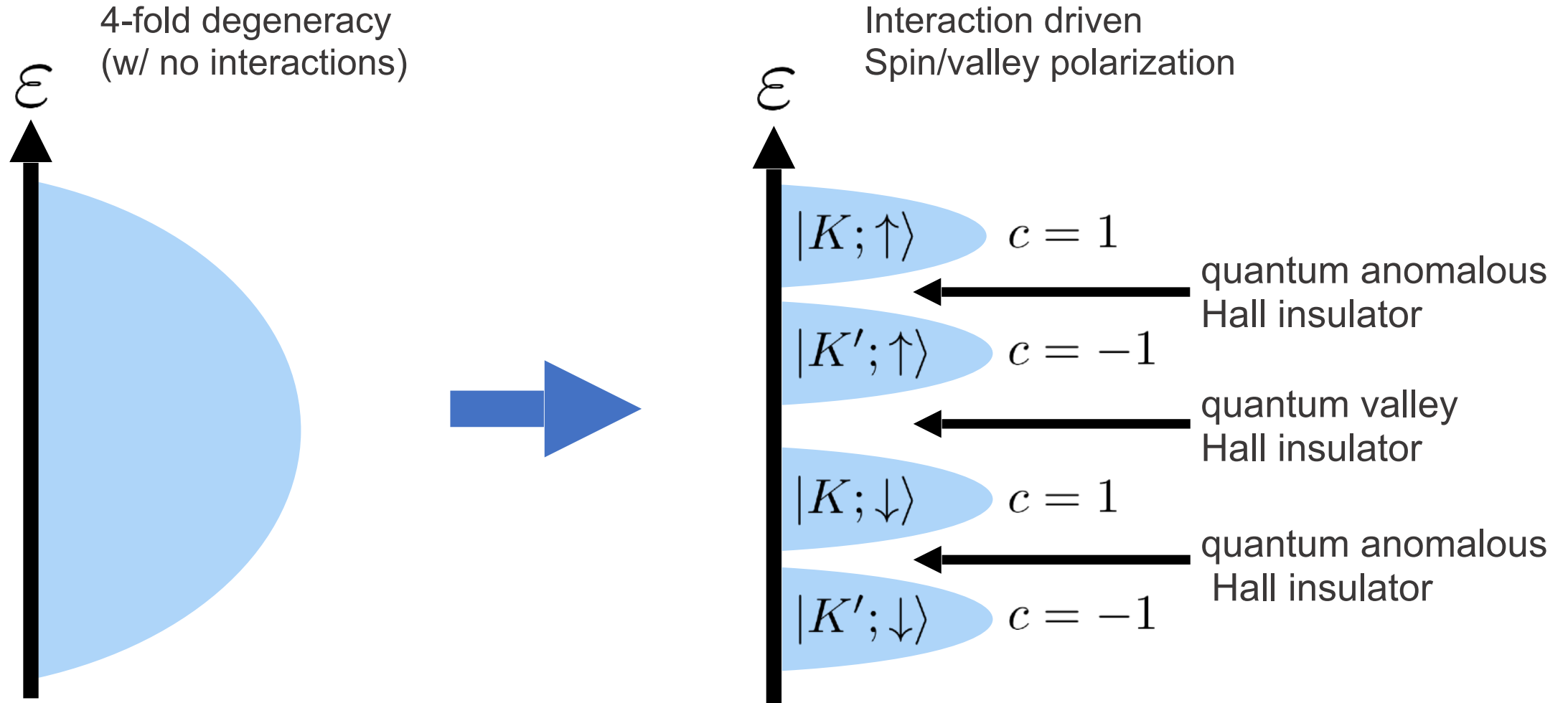


Resistivity: no strong feature at 3/4



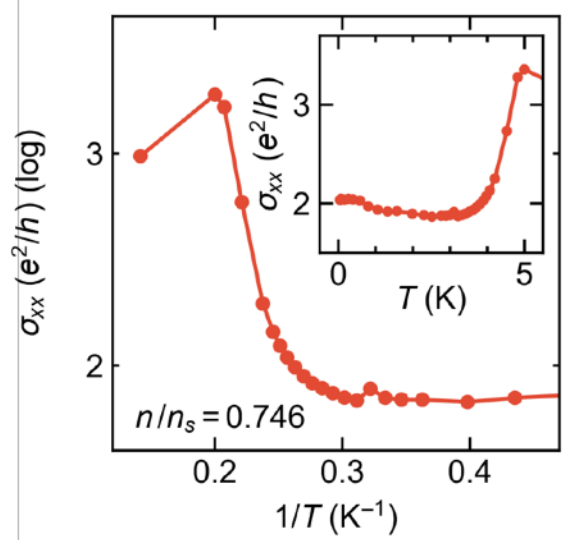
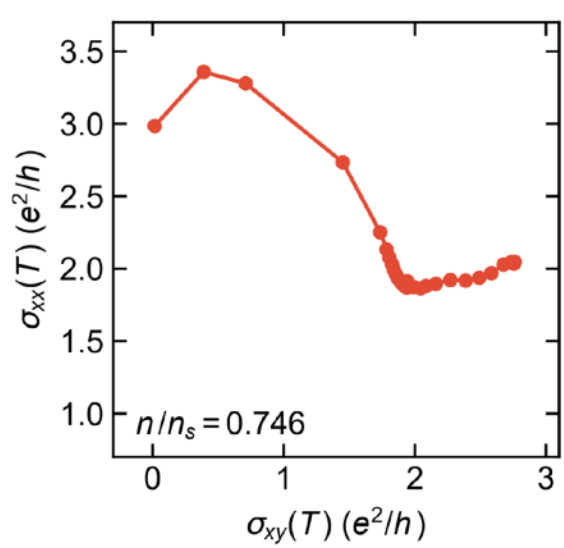
Nature of Emergent Ferromagnetism at $\frac{3}{4}$ Filling?

Simplistic band diagram: What *might* be happening...



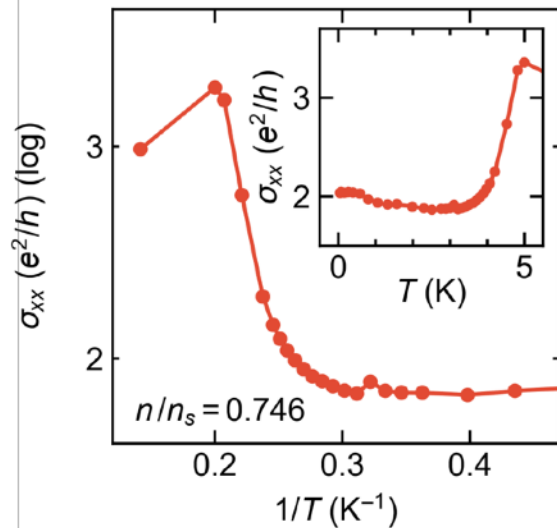
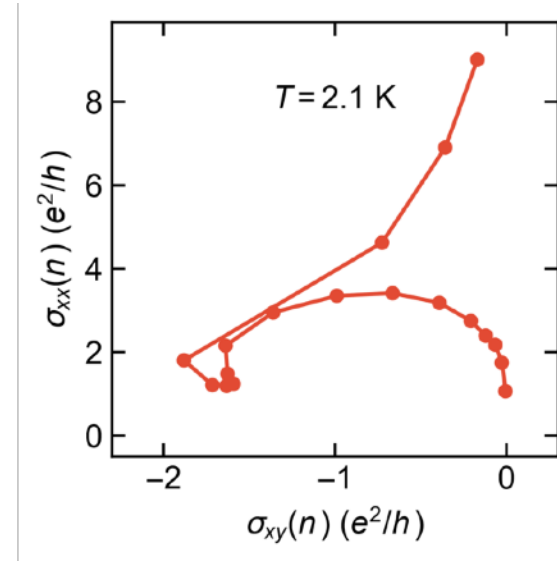
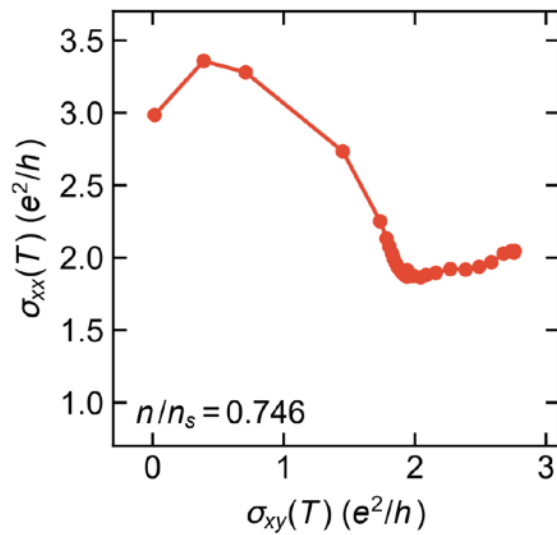
Nature of Emergent Ferromagnetism

Intrinsic vs. extrinsic anomalous Hall mechanisms



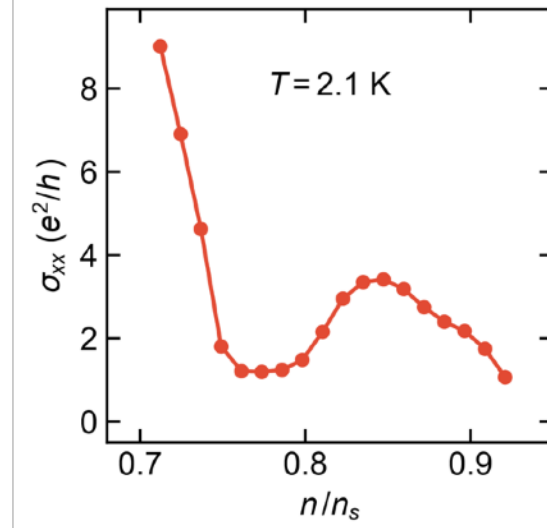
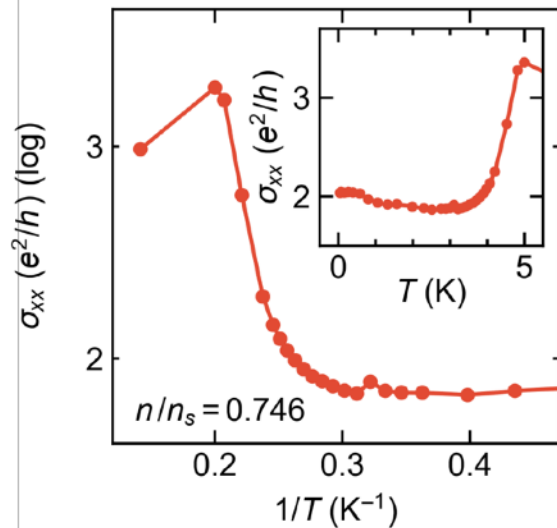
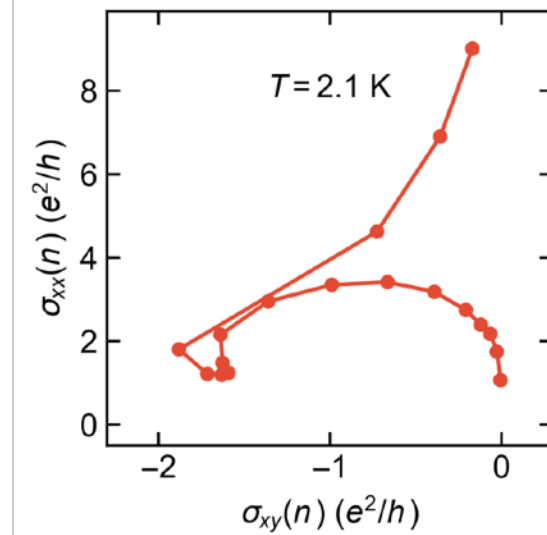
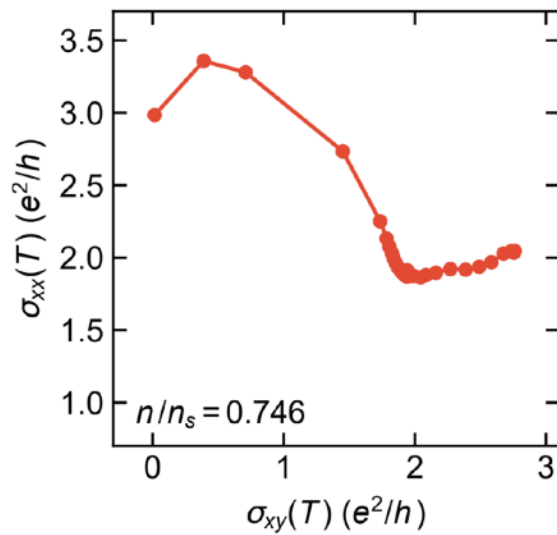
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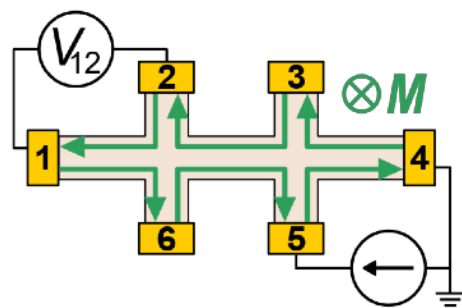
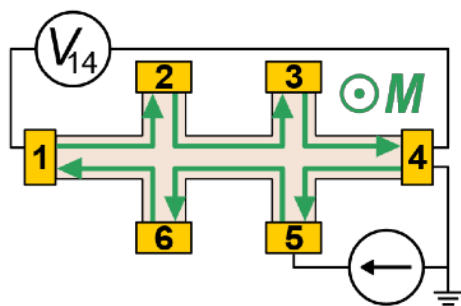


Nature of Emergent Ferromagnetism

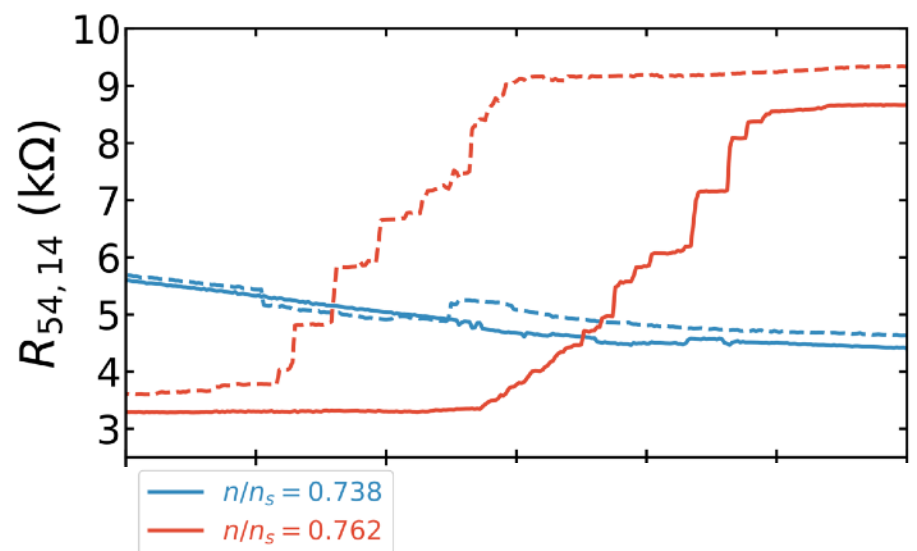
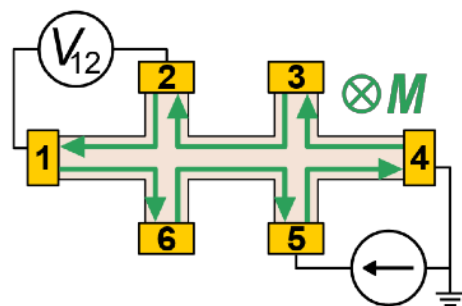
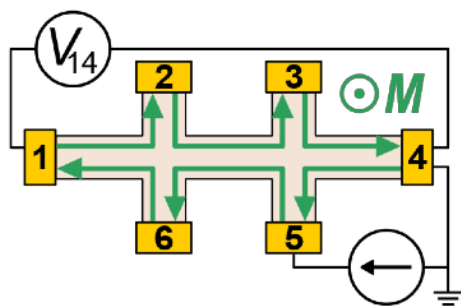
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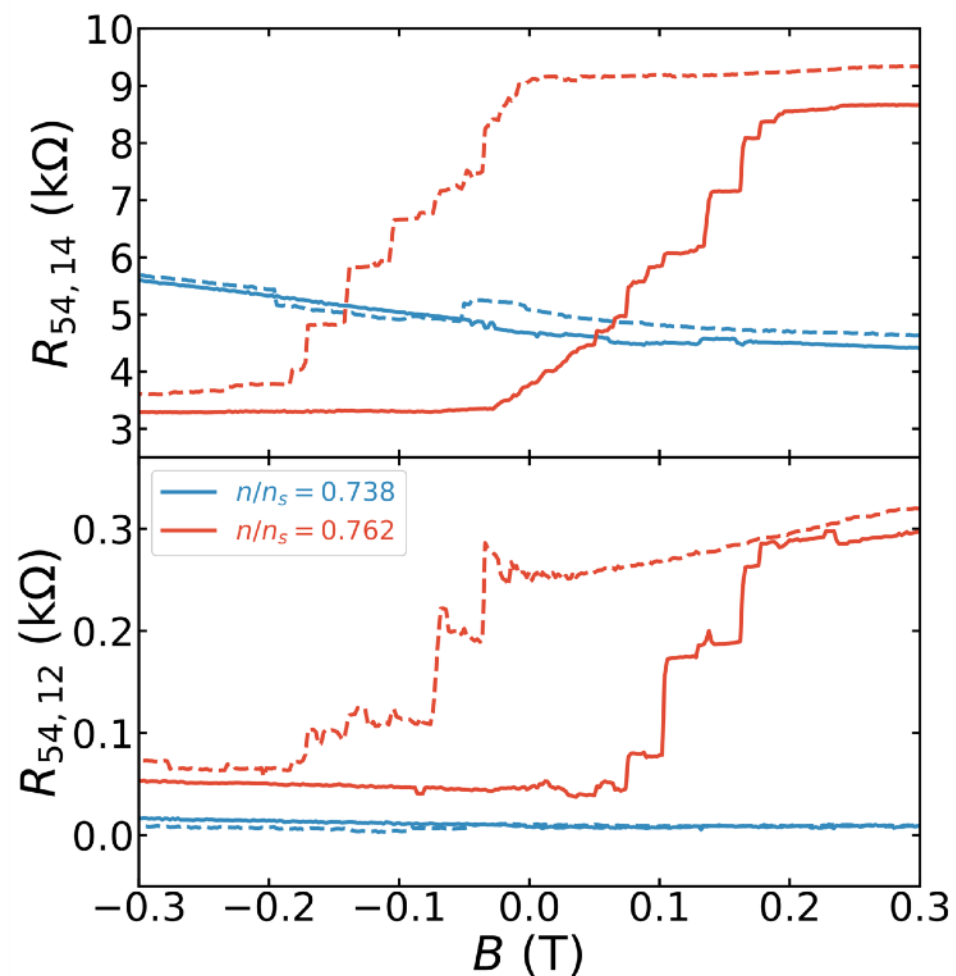
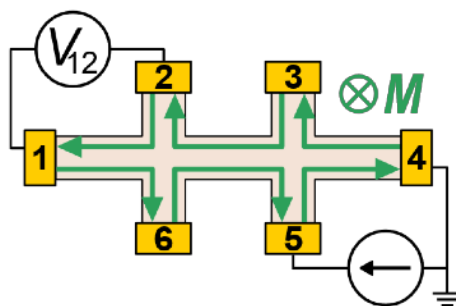
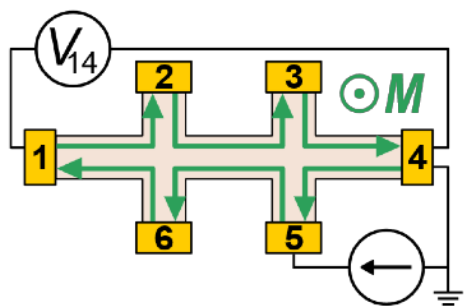
3- and 4-Terminal Nonlocal Transport at $\frac{3}{4}$ Filling



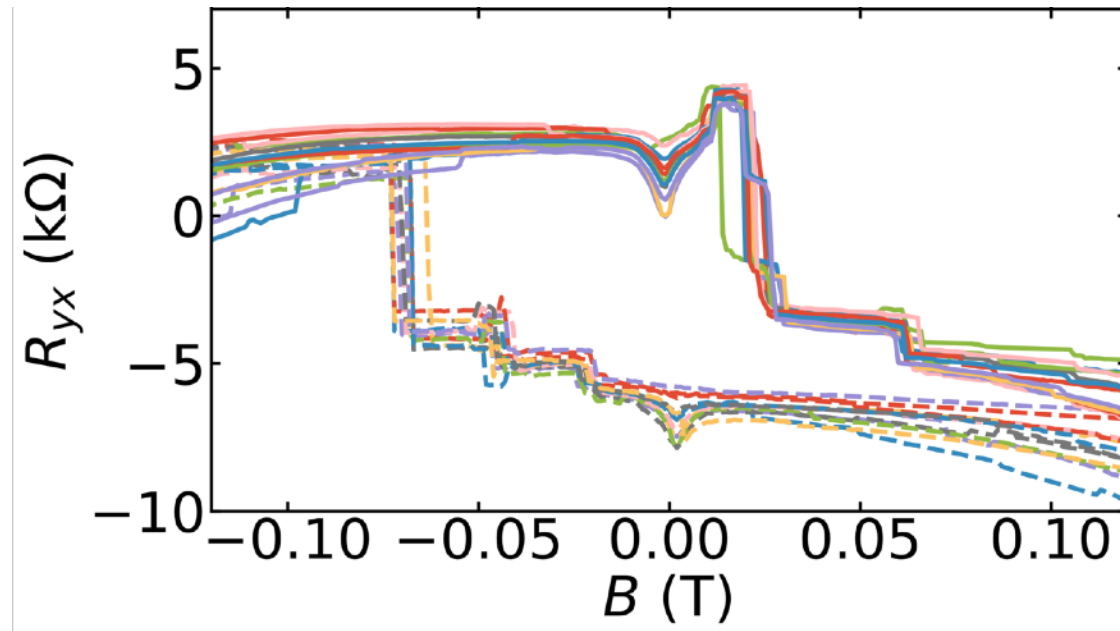
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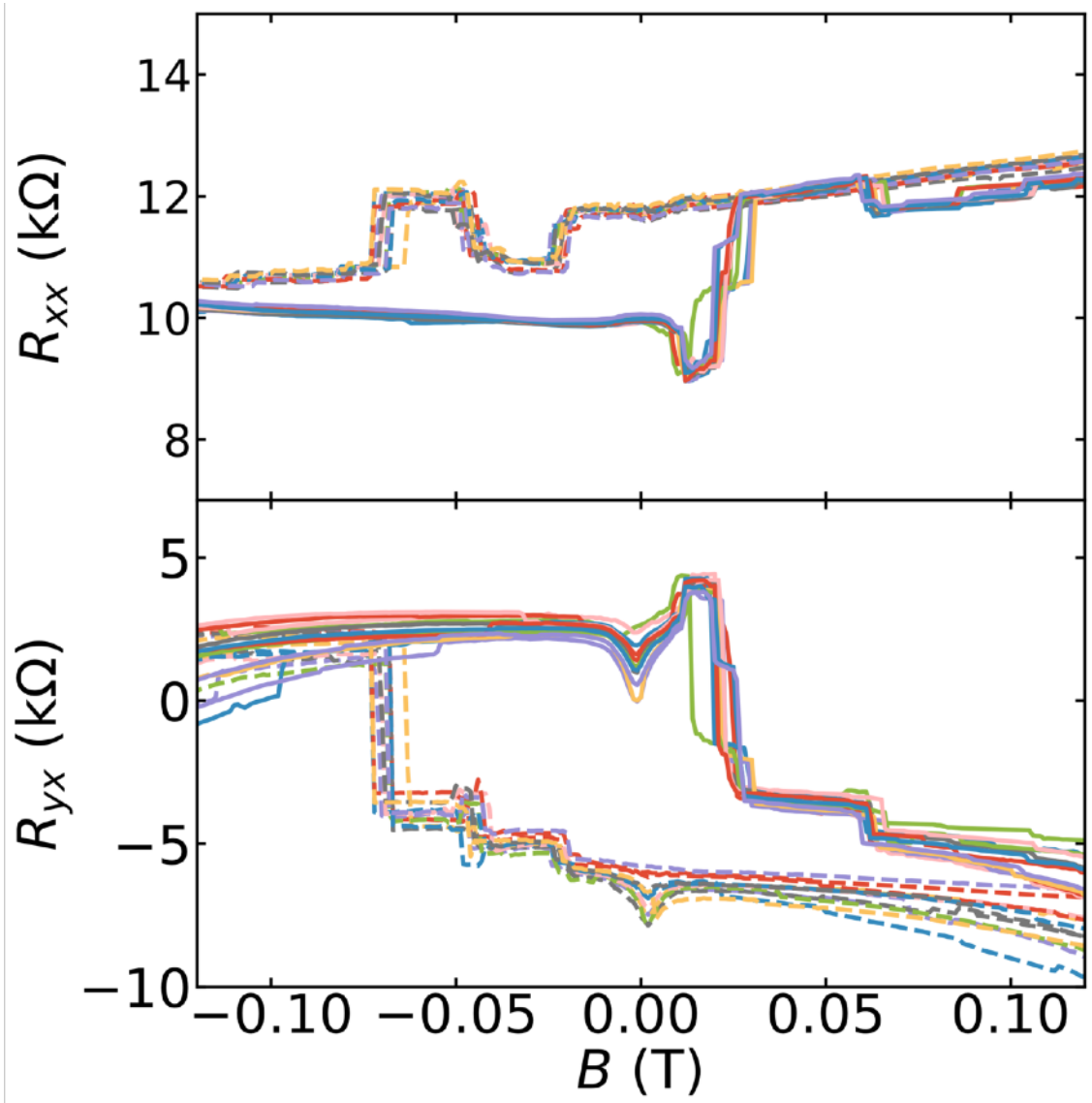
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Repeatable Hysteresis Fine Structure in Field

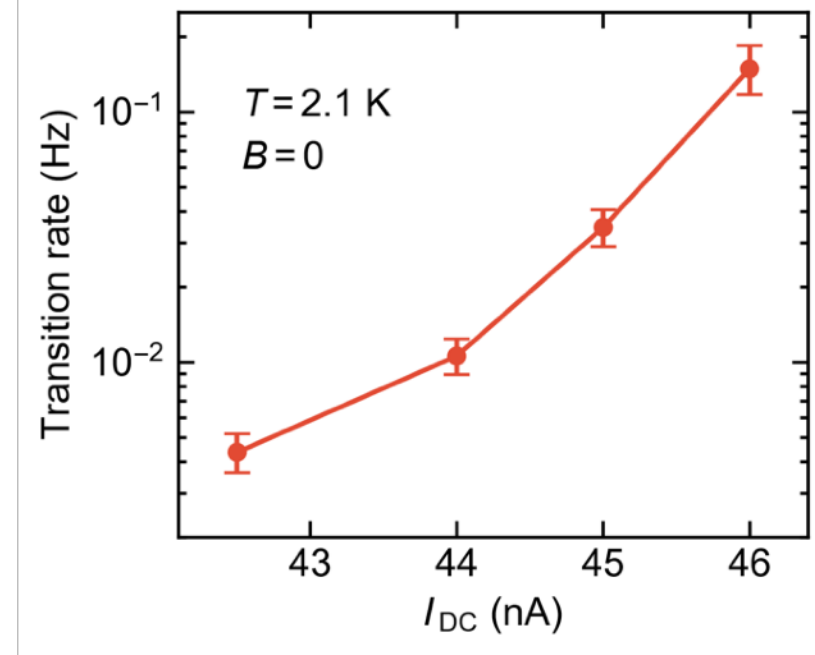
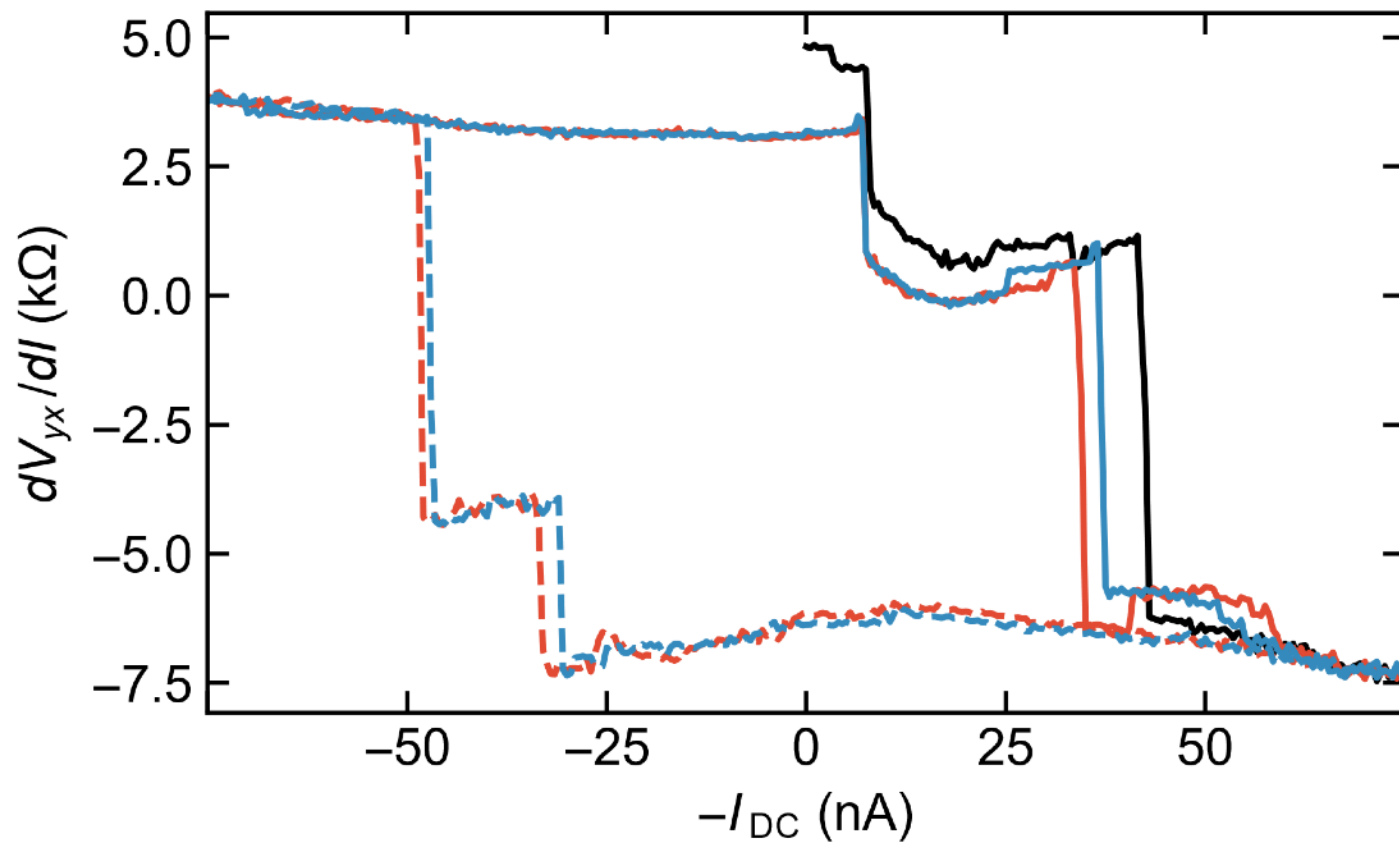


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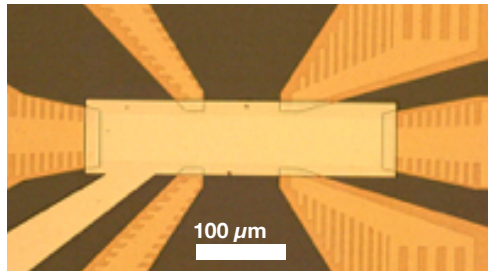


Repeatable Hysteresis in Current

Dynamics of transition appear memoryless

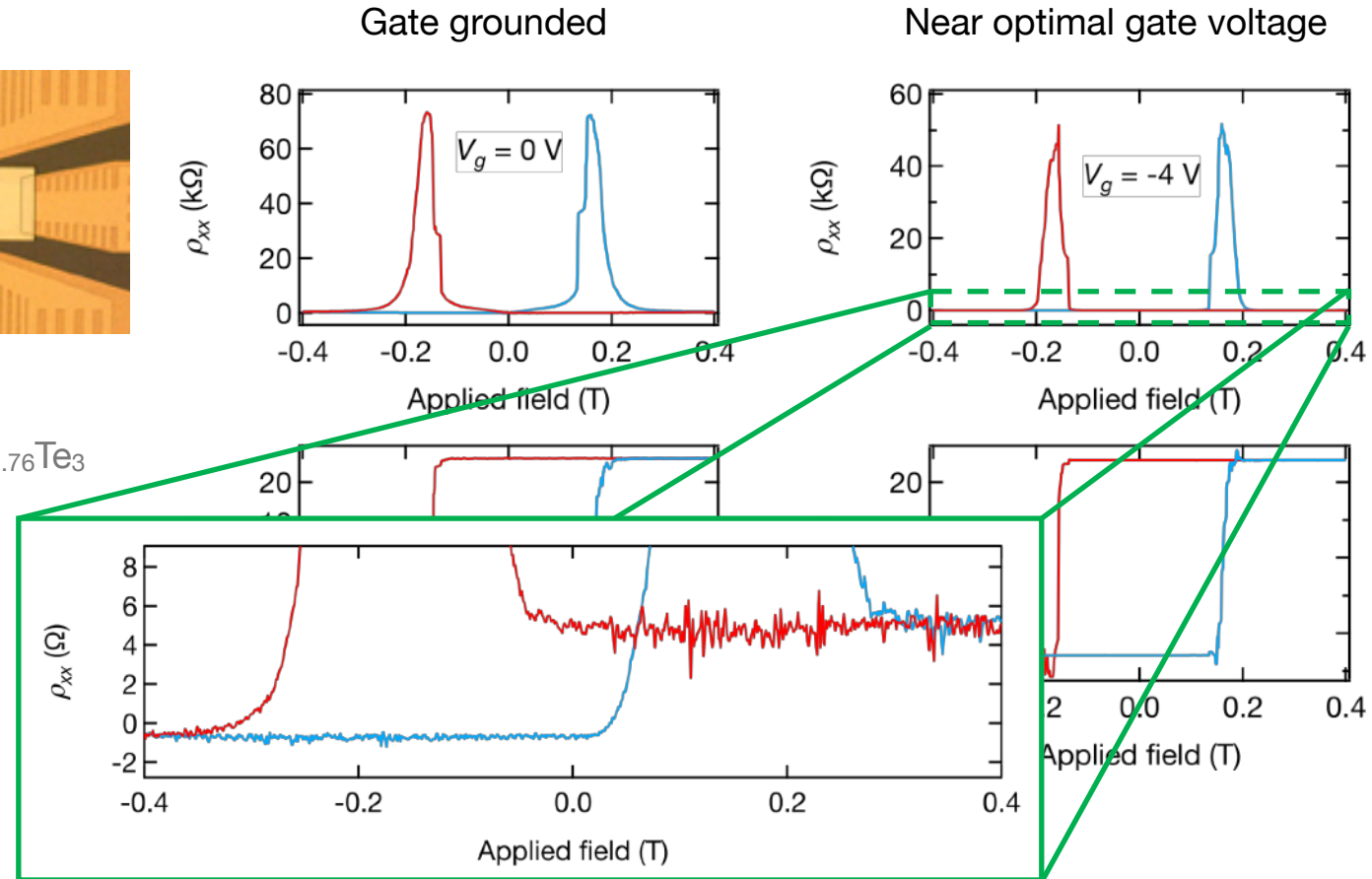


Comparison: Quantum Anomalous Hall in $(\text{Cr,Bi,Sb})_2\text{Te}_3$



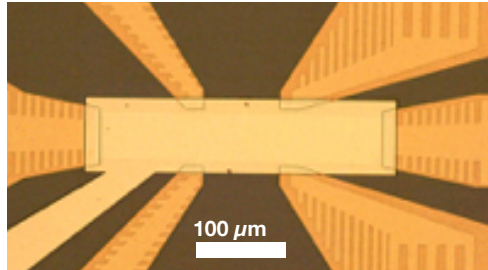
Material & device:

6 QL $\text{Cr}_{0.24}(\text{Bi}_{0.3}\text{Sb}_{0.7})_{1.76}\text{Te}_3$
GaAs substrate
Ti/Au contacts
Top gate



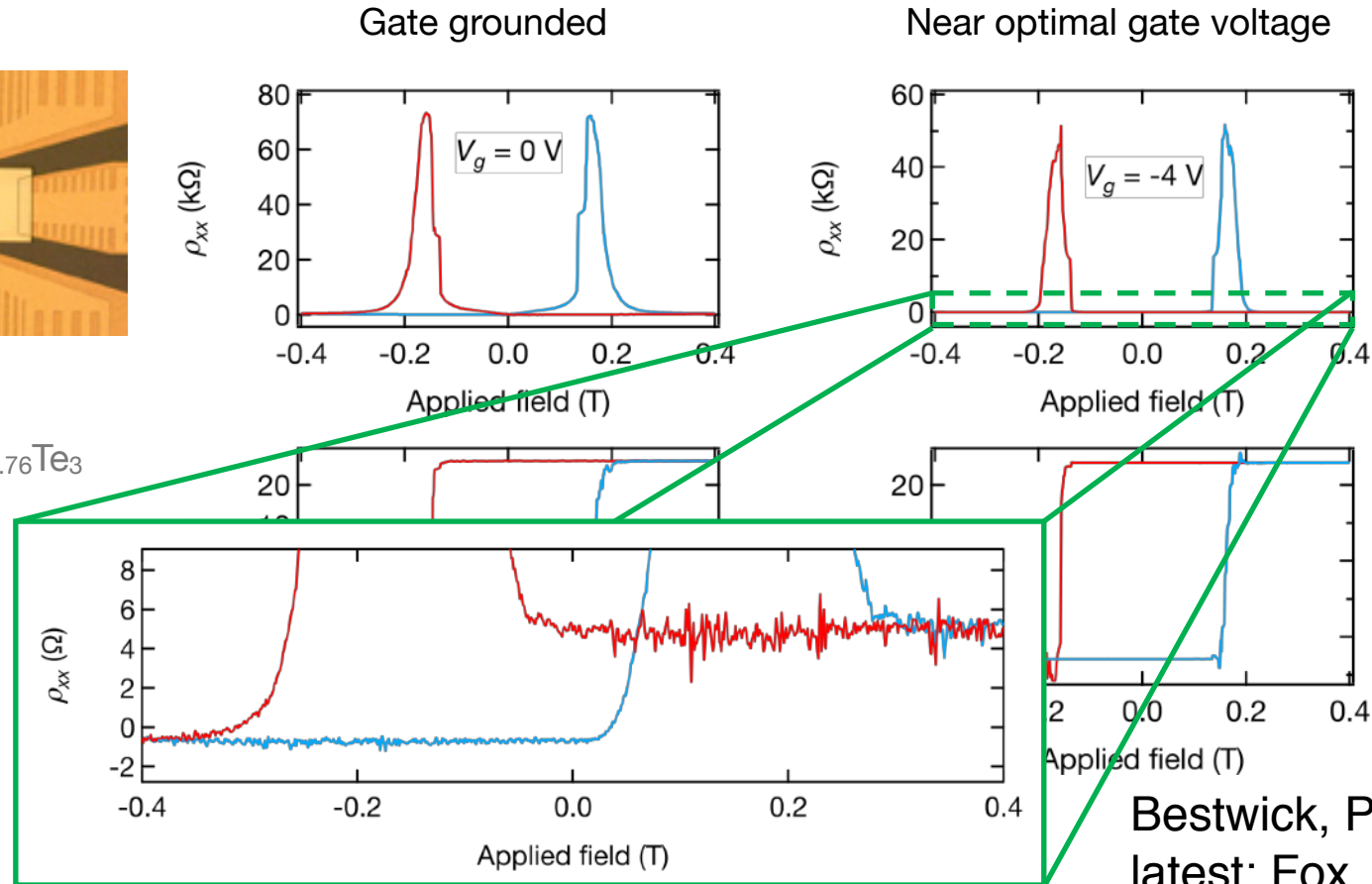
Systematic offsets due to finite input impedance of voltage preamplifiers

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Systematic offsets due to finite input impedance of voltage preamplifiers

Bestwick, PRL 114, 187201 (2015)
 latest: Fox, PRB 98.075145 (2020)
 Rex 2 parts in 10 million
 Rhoxy 20 m Ω

Acknowledgements

DGG Group @ Stanford

Aaron Sharpe

Eli Fox

Ilan Rosen

Andrew Bestwick

UCLA (Magnetic TIs)

Kang Wang

Xufeng Kou

Lei Pan

DOE: SIMES Spin

Physics and Nanoscale

Probes FWP

Marc Kastner

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Questions?

